

TOSHIBA

Serial Interface NAND

Technical Data Sheet

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TOSHIBA

Storage & Electronic Devices Solutions
Memory Division

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1. Introduction

1.1. General Description

The TC58CVG2S0HRAIG is a serial interface NAND Flash for embedded applications which supports the SPI interface.

The TC58CVG2S0HRAIG is organized as $(4096 + 128)$ bytes \times 64 pages \times 2048 blocks. The device has a 4224 byte data buffer which allows program and read data to be transferred between the buffer and the memory cell array in 4224-byte increments. The Erase Operation is implemented in a single block unit (256 Kbytes + 8 Kbytes: 4224 bytes \times 64 pages). The device has the high speed mode for sequential Page Read Operation. When high speed mode is enabled, the average of tR is shortened.

The TC58CVG2S0HRAIG has ECC logic on the chip and 8bit read errors for each (512 bytes + 16 bytes) can be corrected. The internal ECC logic has detailed bit flip count report.

1.2. Definitions and Abbreviations

SPI

Serial Peripheral Interface.

Address

The address is comprised of a column address (CA) with 13bits and a row address (RA) with 17bits. The row address identifies the page and block to be accessed. The column address identifies the byte within a page to access.

Column

The byte location within the page.

Row

Refer to the block and page to be accessed.

Sector

The 512 bytes unit in a page.

Page

The smallest addressable unit for the Read and the Program operations.

Block

Consists of multiple pages and is the smallest addressable unit for the Erase Operation.

Data Buffer

Buffer used to transfer data to and from the cell array.

Cell Array

Memory cell of NAND flash

Device

The packaged NAND unit.

1.3. Features

- **Organization**

Organization (Internal ECC is enabled, default)

Memory Cell Array	4224 × 64 × 2048 × 8 bits
Data Buffer	4224 × 8 bits
Page Size	4224 bytes
Block Size	(256K + 8K) bytes

Organization (Internal ECC is disabled)

Memory Cell Array	4352 × 64 × 2048 × 8 bits
Data Buffer	4352 × 8 bits
Page Size	4352 bytes
Block Size	(256K + 16K) bytes

- **ECC**

8 bit ECC for each 512bytes is required. The device has ECC logic internally.

- **Mode**

Page Read, Page Program, Block Erase, Internal Data Move, Reset, Write Enable, Write Disable, Block Lock, Get Feature, Set Feature, Block Protection, Parameter Page Read, Read ID, Read Unique ID

- **Power Supply**

V_{CC} = 2.7 V to 3.6 V

- **Access Time**

Cell Array to Data Buffer	280 μs max
	115 μs typ
Data Transfer rate	104 MHz max

- **Program/Erase Time**

Programming Time	450 μs/page typ
Block Erasing Time	2.0 ms/block typ

- **Operating Current**

Read Operation Current with HSE on (Average)	21 mA max
Read Operation Current with HSE off (Average)	15 mA max
Program Operation Current (Average)	18 mA max
Erase Operation Current (Average)	22 mA max
Standby Current	180 μA max
	35 uA typ

- **Reliability**

Refer to reliability note.

- **Package**

WS0N8

2. Memory Organization

2.1. Pin Descriptions

Table 1 Pin Descriptions

Pin Name	Pin Function
\overline{CS}	Chip Select
SO/SO1	Serial Data Output / Serial Data Output 1
$\overline{WP}/SO2$	Write Protect / Serial Data Output 2
SI/SO0	Serial Data Input / Serial Data Output 0
HOLD/SO3	Hold Input / Serial Data Output 3
SCK	Serial Clock Input
VCC	Power Supply
VSS	Ground

Note:

If the \overline{WP} pin is low and BRWD bit is set to 1, the overwrite for the BRWD(bit [7]) and the BL bits (bits [5:3]) in address A0h of the feature table shown in Table 12 is prohibited.

The users cannot drive the \overline{WP} pin while \overline{CS} pin is low.

The HOLD pin and the \overline{WP} pin are pull up to VCC internally.

2.2. Pin Assignment (Top View)

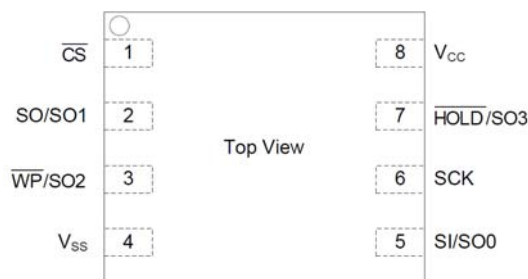


Figure 1. WSON Pin Assignment (Top View)

2.3. Block Diagram

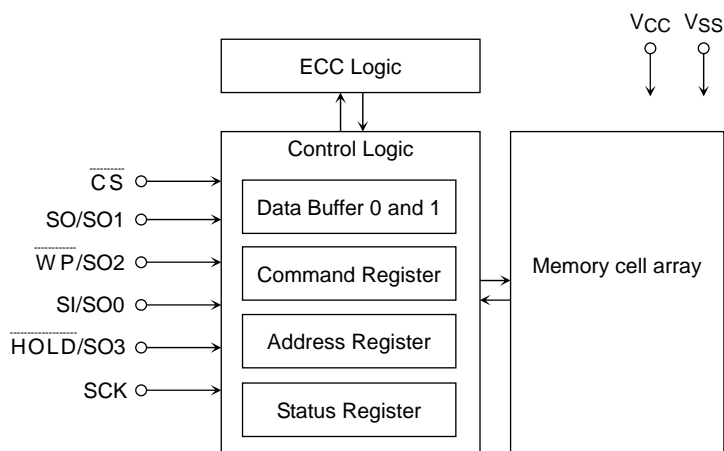


Figure 2. Block Diagram

2.4. Cell Layout

The Program Operation works on page units while the Erase Operation works on block units.

When internal ECC is turned ON the default setting, a page consists of 4224 bytes in which 4096 bytes are used for main memory storage and 128 bytes are used for redundancy or for other uses. In the case that internal ECC is turned OFF, the redundancy area will be expanded to 256 bytes automatically.

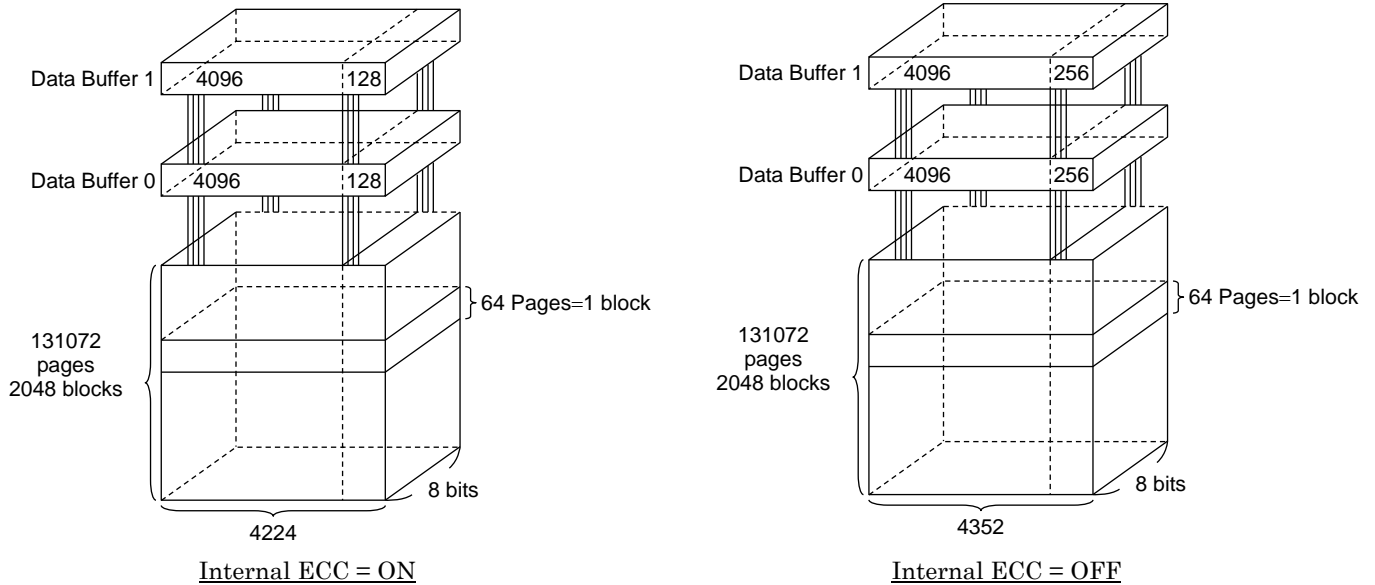
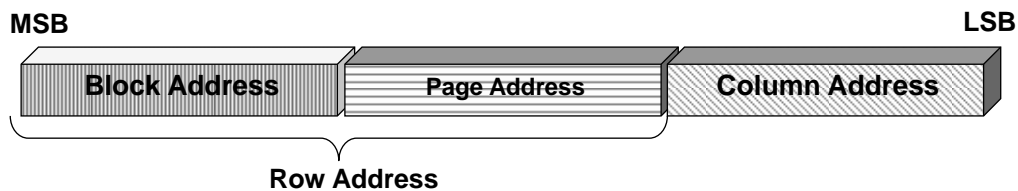


Figure 3. Cell Layout

2.5. Addressing

There are two address types used: the column address and the row address. The column address is used to access bytes within a page. The row address is used to address pages and blocks. There are some functions that may require only row addresses, such as Block Erase.



Row Address: 17 bits

Block Address (2048 blocks/device): 11 bits

Page Address (64 pages/block): 6 bits

Column Address: 13 bits

Column Address (4224 or 4352 bytes/page): 13 bits

Figure 4. Addressing

2.6. Valid Blocks

Table 2 Valid Blocks

Symbol	Parameter	Min.	Typ.	Max.	Unit
N _{VB}	Number of Valid Blocks	2008	-	2048	Block

Note:

The device occasionally contains unusable blocks.

The first block (Block 0) is guaranteed to be a valid block at the time of shipment.

The specification for the minimum number of valid blocks is applicable over the lifetime

3. Physical Interface

3.1. Absolute Maximum Rating

Stresses greater than those listed in Table 3 may cause permanent damage to the device. This is a stress rating only.

Table 3 Absolute Maximum Rating

Symbol	Parameter	Value	Unit
V _{CC}	Power Supply Voltage	-0.3 to 3.9	V
V _{IN}	Input Voltage	-0.3 to V _{CC} + 0.3 (≤ 3.9 V)	V
V _{I/O}	Input /Output Voltage	-0.3 to V _{CC} + 0.3 (≤ 3.9 V)	V
PD1	Power Dissipation 1	0.42	W
PD2	Power Dissipation 2 (WSON ePAD without solder)	0.27	W
T _{SOLDER}	Soldering Temperature (10 s)	260	°C
T _{STG}	Storage Temperature	-55 to 150	°C
T _{OPR}	Operating Temperature	-40 to 85	°C

3.2. Capacitance

Table 4 Capacitance (T_{OPR} = 25°C, f = 1MHz)

Symbol	Parameter	Condition	Min.	Max.	Unit
C _{IN}	Input	V _{IN} = 0 V	-	2.5	pF
C _{OUT}	Output	V _{OUT} = 0 V	-	4	pF

Note: This parameter is periodically sampled and is not tested for every device.

3.3. Recommended DC Operating Conditions

Table 5 Recommended DC Operating Condition

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Power Supply Voltage	2.7	-	3.6	V
V _{IH}	High Level input Voltage	V _{CC} × 0.8	-	V _{CC} + 0.3	V
V _{IL}	Low Level Input Voltage	-0.3	-	V _{CC} × 0.2	V

3.4. Signal Timing

The device supports SPI mode 0 and mode 3. Input data is latched at the rising edge of SCK and data is output at the falling edge of SCK for mode 0 and 3. When $\overline{\text{HOLD}}$ goes Low, the communication is held. The hold state begins the falling edge of SCK.

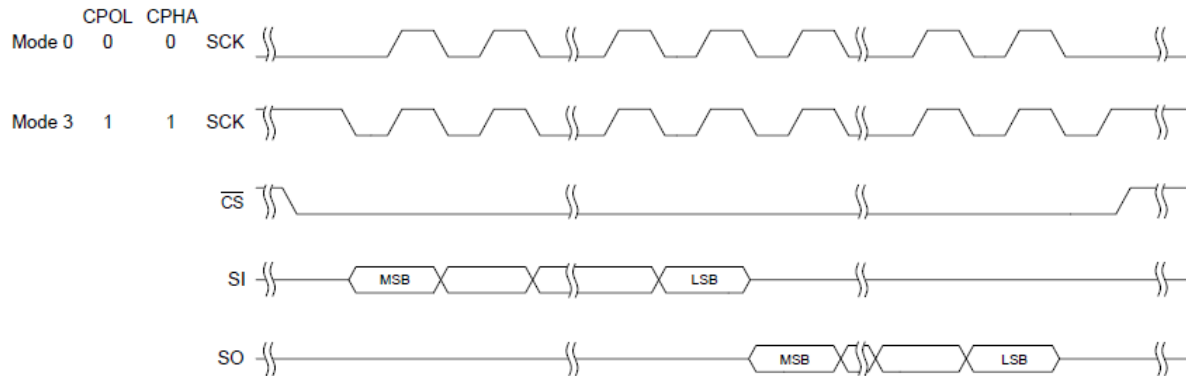
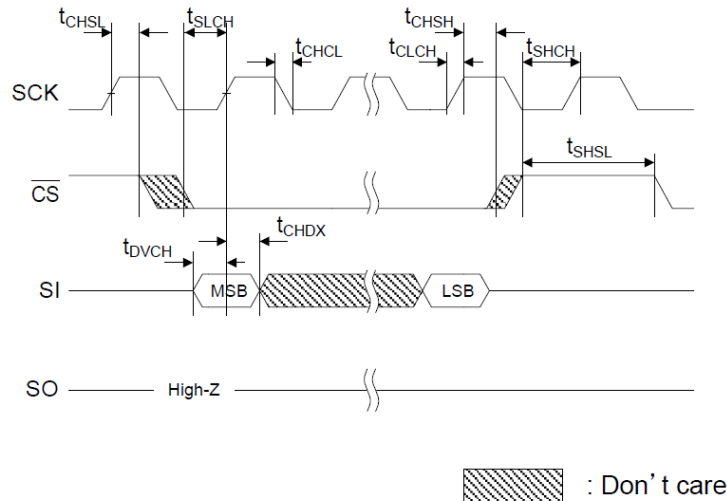
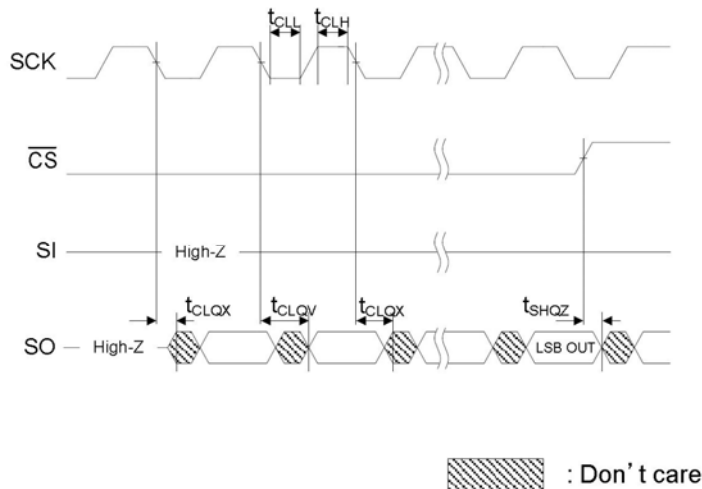


Figure 5. SPI Timing



▨ : Don't care

Figure 6. Serial Input Timing



▨ : Don't care

Figure 7. Serial Output Timing

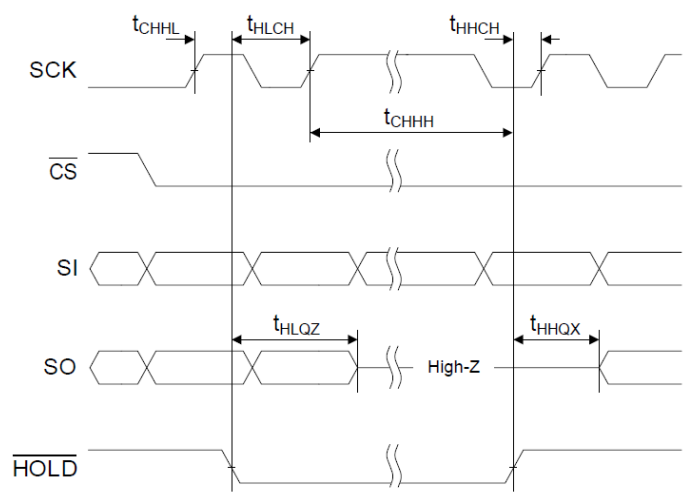


Figure 8. Hold Timing

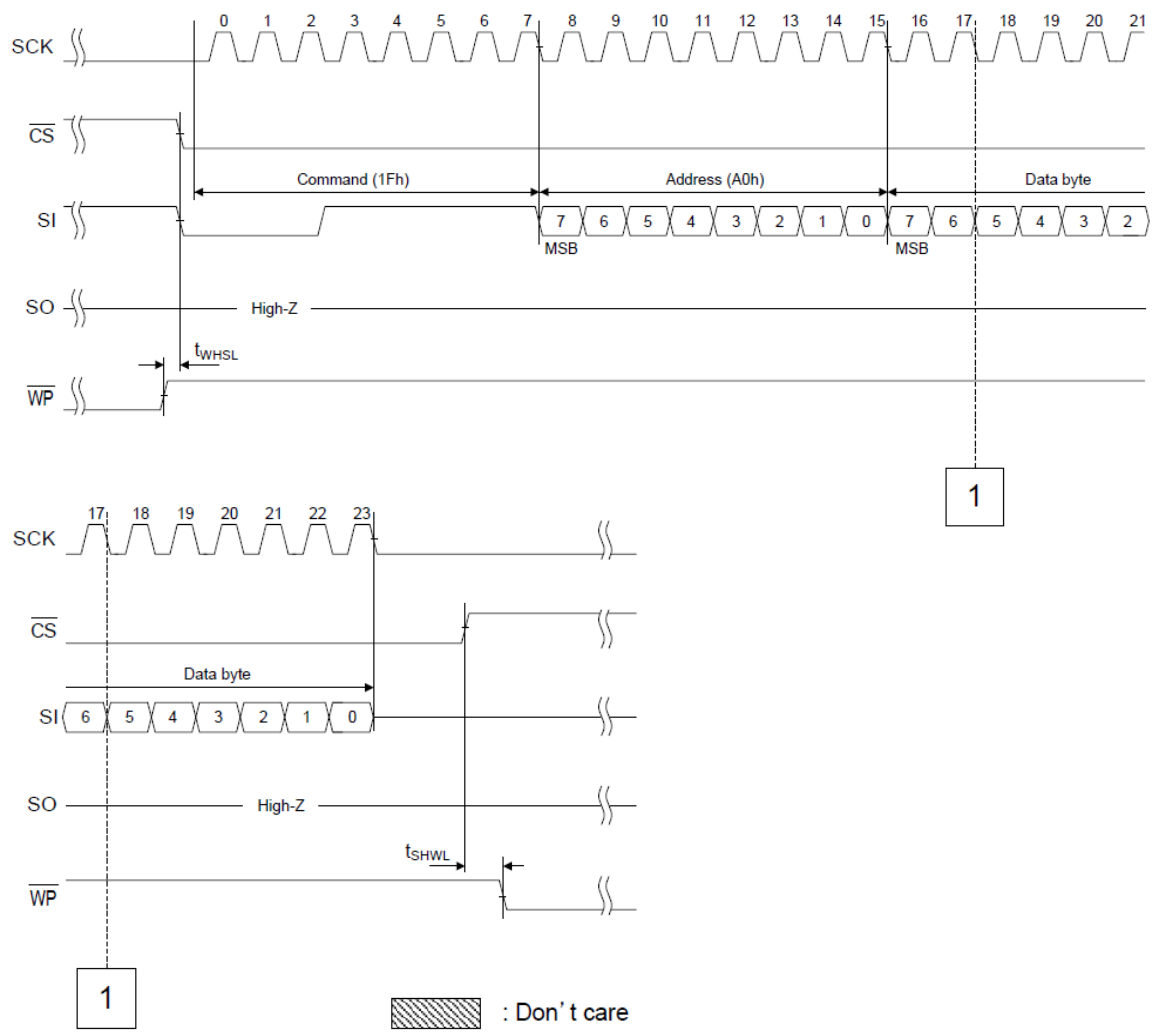


Figure 9. WP Timing (Example)

3.5. AC Characteristics

Table 6 AC Characteristics ($T_{OPR} = -40$ to 85°C , $V_{CC} = 2.7$ to 3.6V)

Symbol	Parameter	Min.	Typ.	Max.	Unit
F_C	Serial Clock Frequency For: all command	-	-	104	MHz
t_{CLH}	Serial Clock High Time	4.5	-	-	ns
t_{CLL}	Serial Clock Low Time	4.5	-	-	ns
t_{CLCH}	Serial Clock Rise Time (Slew Rate)	0.1	-	-	V/ns
t_{CHCL}	Serial Clock Fall Time (Slew Rate)	0.1	-	-	V/ns
t_{SLCH}	CS Active Setup Time	4.6	-	-	ns
t_{CHSH}	CS Active Hold Time	5	-	-	ns
t_{SHCH}	CS Not Active Setup Time	5	-	-	ns
t_{CHSL}	CS Not Active Hold Time	5	-	-	ns
t_{SHSL} / t_{CS}	CS High Time	100	-	-	ns
t_{SHQZ}	Output Disable Time	-	-	20	ns
t_{CLQX}	Output Hold Time	1	-	-	ns
t_{DVCH}	Data In Setup Time	2	-	-	ns
t_{CHDX}	Data In Hold Time	5	-	-	ns
t_{HLCH}	HOLD Low Setup Time (relative to Clock)	5	-	-	ns
t_{HHCH}	HOLD High Setup Time (relative to Clock)	5	-	-	ns
t_{CHHL}	HOLD High Hold Time (relative to Clock)	5	-	-	ns
t_{CHHH}	HOLD Low Hold Time (relative to Clock)	5	-	-	ns
t_{HLQZ}	HOLD Low To High-Z Output	-	-	7	ns
t_{HHQX}	HOLD High To Output	-	-	7	ns
t_{CLQV}	Clock Low To Output Valid	-	-	7.0(CL=10pF) 7.5(CL=20pF) 8.0(CL=30pF)	ns
t_{WHSL}	WP Setup Time Before CS Low	20	-	-	ns
t_{SHWL}	WP Hold Time After CS High	100	-	-	ns
t_{RST}	Device Reset Time (Ready/Read/Program/Erase)	-	-	5/6/10/500	μs

3.6. DC Operating Characteristics

Table 7 DC & Operating Characteristics ($T_{OPR} = -40$ to 85°C , $V_{CC} = 2.7$ to 3.6V)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
I_{IL}	Input Leakage Current	$V_{IN} = 0\text{V to } V_{CC}$	-	-	± 10	μA
I_{LO}	Output Leakage Current	$V_{OUT} = 0\text{V to } V_{CC}$	-	-	± 10	μA
$ICCOA1$	Read Operation Current (Average)	$F_C = 104\text{MHz}$ High Speed Mode = Enable Read Buffer Command : 03h or 0Bh (x1)	-	-	21	mA
$ICCOA2$	Read Operation Current (Average)	$F_C = 104\text{MHz}$ High Speed Mode = Disable Read Buffer Command : 03h or 0Bh (x1)	-	-	15	mA
$ICCOA3$	Program Operation Current (Average)	$F_C = 104\text{MHz}$	-	-	18	mA
$ICCOA4$	Erase Operation Current (Average)	$F_C = 104\text{MHz}$	-	-	22	mA
$ICCS$	Standby Current	$\overline{CS} = V_{CC} - 0.2\text{V}$, $\overline{WP} = V_{CC}$, $\text{HOLD} = V_{CC}$	-	35	180	μA
V_{OH}	High Level Output Voltage	$I_{OH} = -0.1\text{mA}$	$V_{CC}-0.2$	-	-	V
V_{OL}	Low Level Output Voltage	$I_{OL} = 0.1\text{mA}$	-	-	0.2	V

Note:

Refer to the High Speed Mode in 4.3.

ICCOA1~ICCOA4 are the average current during the full operation sequence.

3.7. Programming, Reading and Erasing Characteristics

Table 8 Programming, Reading and Erasing Characteristics ($T_{OPR} = -40$ to 85°C , $V_{CC} = 2.7$ to 3.6V)

Symbol	Parameter	Min.	Typ.	Max.	Unit
t_{PROG}	Average Programming Time	-	450	600	μs
N	Number of Partial Program Cycles in the Same Page	-	-	4	time
t_{BERASE}	Block Erasing Time	-	2	7	ms
t_R	Cell Array to the Buffer (with ECC)	-	115	280	μs
t_{RHSA4}	Average Read Time for Sequential Read (High Speed Mode, x4)	-	35	-	μs

Note:

Refer to the data pair of ECC calculation in 4.16 Internal ECC.

Refer to the High Speed Mode in 4.3.

t_{RHSA4} is the average read time of 64 times page read in a block.

3.8. Power ON/OFF Sequence

The timing sequence shown in the figure below is necessary for the power-on/off sequence.

The device internal initialization starts after the power supply reaches an appropriate level in the power on sequence. The users cannot issue any commands while t_{VSL} . From the end of t_{VSL} to the end of t_{VOP} , Get Feature Operation and Reset Operation can be issued. OIP bit in the feature table indicates the busy state in this time period. All operations are available after t_{VOP} .

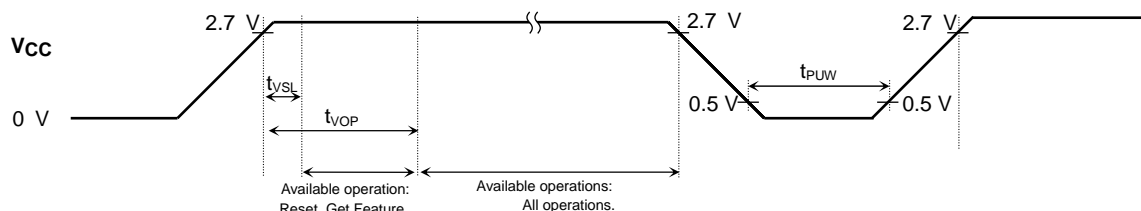


Figure 10. Power ON/OFF Sequence

Table 9 Power on Timing

Symbol	Parameter	Min.	Max.	Unit
t_{VSL}	$V_{CC}(\text{min})$ to CS Low	-	100	μs
t_{VOP}	$V_{CC}(\text{min})$ to all operation	-	1.1	ms
t_{PUW}	Waiting time for power on	1	-	ms
VCCSR	VCC Slew Rate	-	216	mV/ μs

3.9. AC Test Condition

Table 10 AC Test Condition

PARAMETER	CONDITION
	$V_{CC}: 2.7$ to 3.6V
Input level	$V_{CC} \times 0.2$ to $V_{CC} \times 0.8$
Input pulse rise and fall time	2 ns
Input comparison level	$V_{CC} / 2$
Output data comparison level	$V_{CC} / 2$
Output load	C_L (30pF) + 1 TTL

4. Command Description and Device Operation

4.1. Command Set

Table 11 Command Set

Operation	Byte 1 (CMD)	Byte 2	Byte 3	Byte 4	Byte 5	Byte N
Read Cell Array	13h	Dummy + A16 (Input)	A15-A8 (Input)	A7-A0 (Input)	-	-
Read Buffer	03h/0Bh	Dummy + A12-A8 (Input)	A7-A0 (Input)	Dummy	D*-D* (Output)	D*-D* (Output)
Read Buffer x2	3Bh	Dummy + A12-A8 (Input)	A7-A0 (Input)	Dummy	D*-D* (Output)	D*-D* (Output)
Read Buffer x4	6Bh	Dummy + A12-A8 (Input)	A7-A0 (Input)	Dummy	D*-D* (Output)	D*-D* (Output)
Program Load	02h	Dummy + A12-A8 (Input)	A7-A0 (Input)	D*-D* (Input)	D*-D* (Input)	D*-D* (Input)
Program Execute	10h	Dummy + A16 (Input)	A15-A8 (Input)	A7-A0 (Input)	-	-
Protect Execute	2Ah	Dummy + A16 (Input)	A15-A8 (Input)	A7-A0 (Input)	-	-
Program Load Random Data	84h	Dummy + A12-A8 (Input)	A7-A0 (Input)	D*-D* (Input)	D*-D* (Input)	D*-D* (Input)
Block Erase	D8h	Dummy + A16 (Input)	A15-A8 (Input)	A7-A0 (Input)	-	-
Reset	FFh/FEh	-	-	-	-	-
Write Enable	06h	-	-	-	-	-
Write Disable	04h	-	-	-	-	-
Get Feature	0Fh	A7-A0 (Input)	D7-D0 (Output)	D7-D0 (Output)	D7-D0 (Output)	D7-D0 (Output)
Set Feature	1Fh	A7-A0 (Input)	D7-D0 (Input)	-	-	-
Read ID	9Fh	Dummy	ID (Output)	ID (Output)	-	-

Note:

- 1) Input of a command other than those specified in Table 11 is prohibited. Stored data may be corrupted if an unknown command is entered during the command cycle.
- 2) During the operation in progress, do not input any command except 0Fh, FFh and FEh.
- 3) The user can issue the Protect Execute (2Ah) only one time for each block.
- 4) Once the Get Feature command is issued, the status and setting information are outputted continuously.

4.2. Page Read Operation

The Read Cell Array and Read Buffer commands are required to read the data in a page. The Read Cell Array command reads the page data from the NAND cell array to the data buffer. The Read Buffer command reads the data from the data buffer. The operation sequence is as follows.

1. Read Cell Array (13h) : To read the data from the cell array to the internal data buffer.
2. Get Feature (0Fh) : To read the status of the device.
3. Read Buffer (03h or 0Bh) : To output the data from the internal data buffer.
or Read Buffer x2 (3Bh)
or Read Buffer x4 (6Bh)

Read Buffer, Read Buffer x2 and Read Buffer x4 commands are repeatable commands.

For the Read Buffer x2 and Read Buffer x4 read modes are available as shown in Figure 13 and Figure 14.

4.2.1. Read Cell Array (13h)

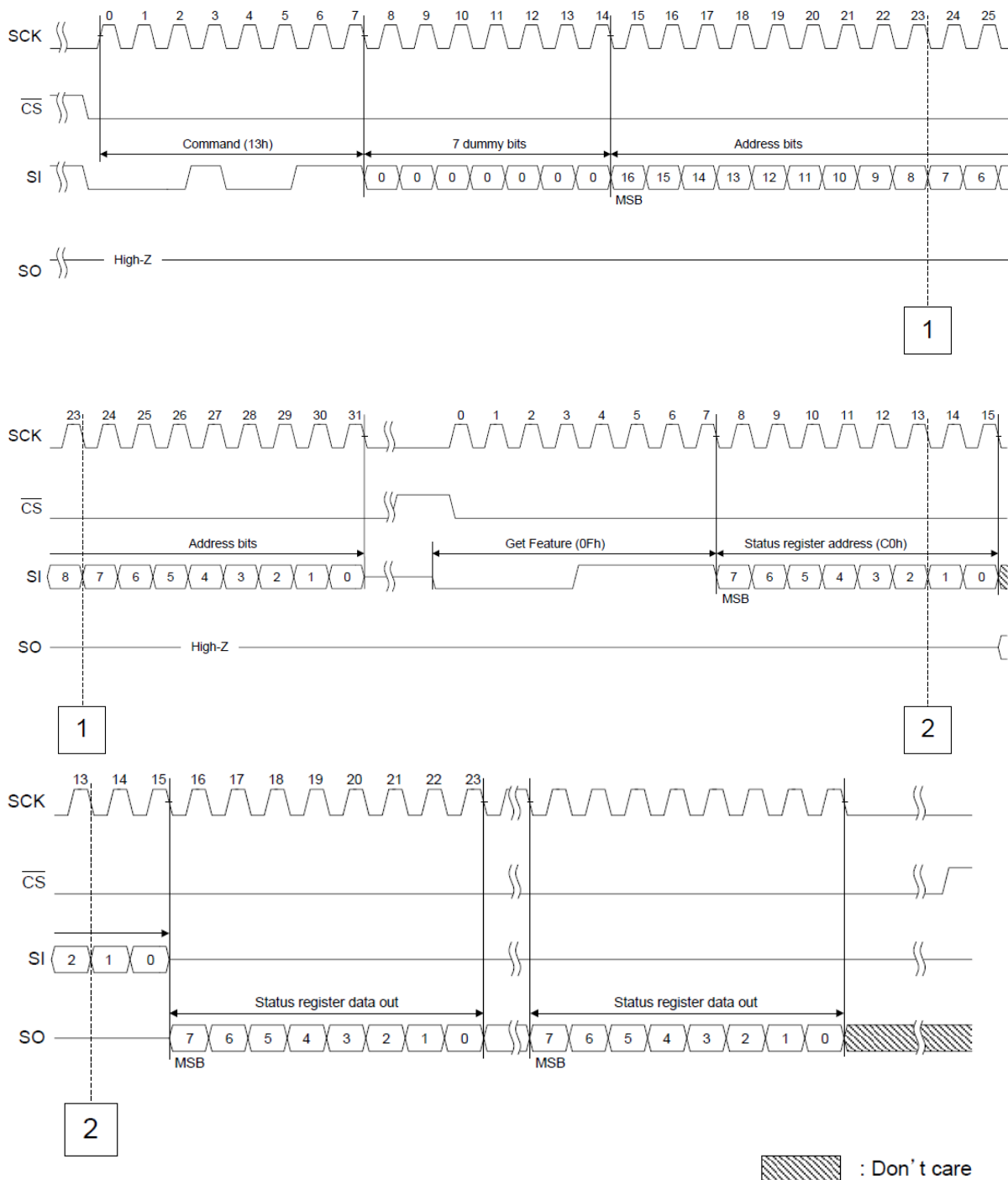
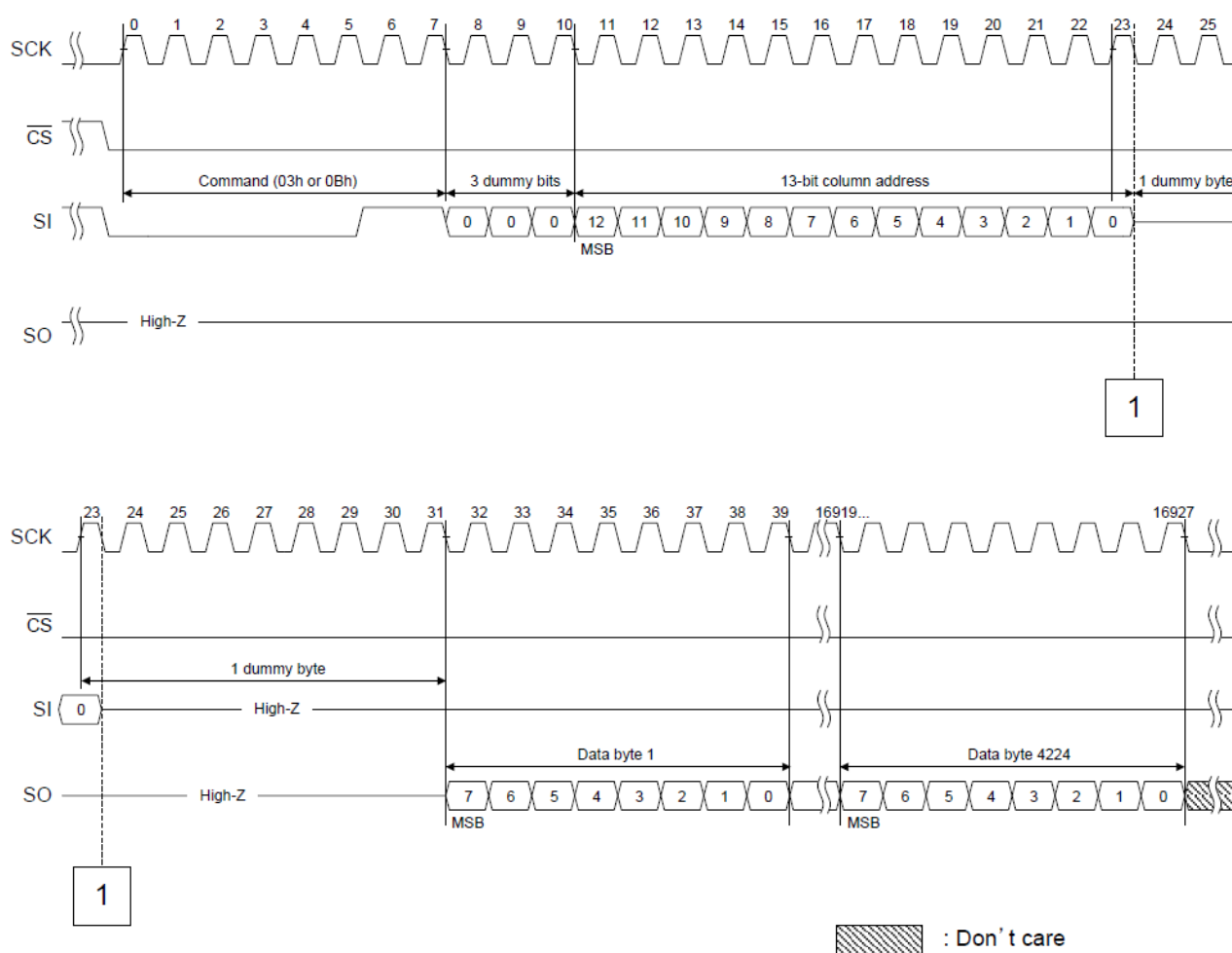


Figure 11. Page Read from Cell Array to Buffer

4.2.2. Read Buffer (03h or 0Bh)

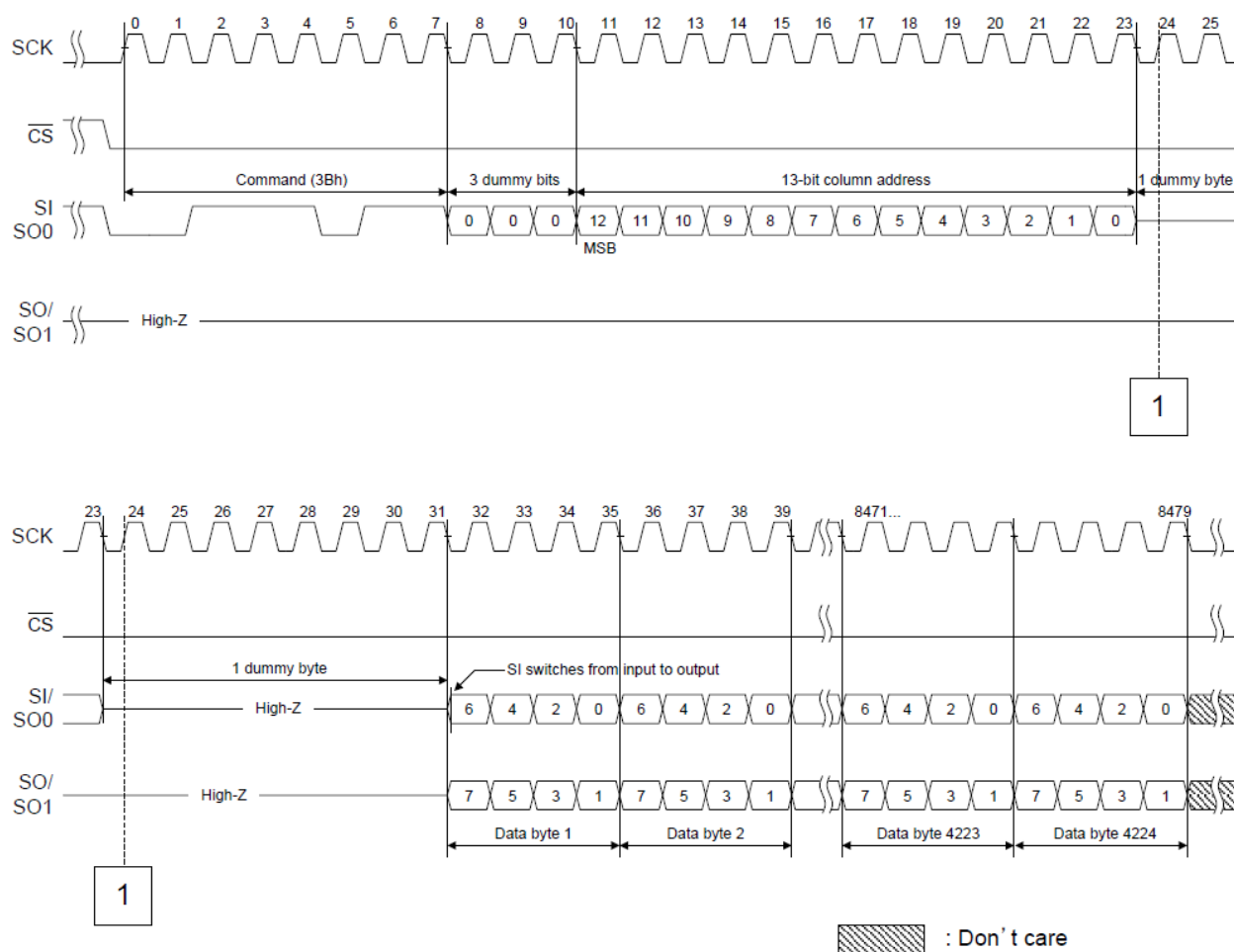


Note:

When internal ECC is turned OFF, the maximum output data size is 4352 Bytes.

Figure 12. Page Read from Buffer Timing

4.2.3. Read Buffer x2 (3Bh)



Note:

When internal ECC is turned OFF, the maximum output data size is 4352 Bytes.

Figure 13. Page Read from Buffer x2 Timing

4.2.4. Read Buffer x4 (6Bh)

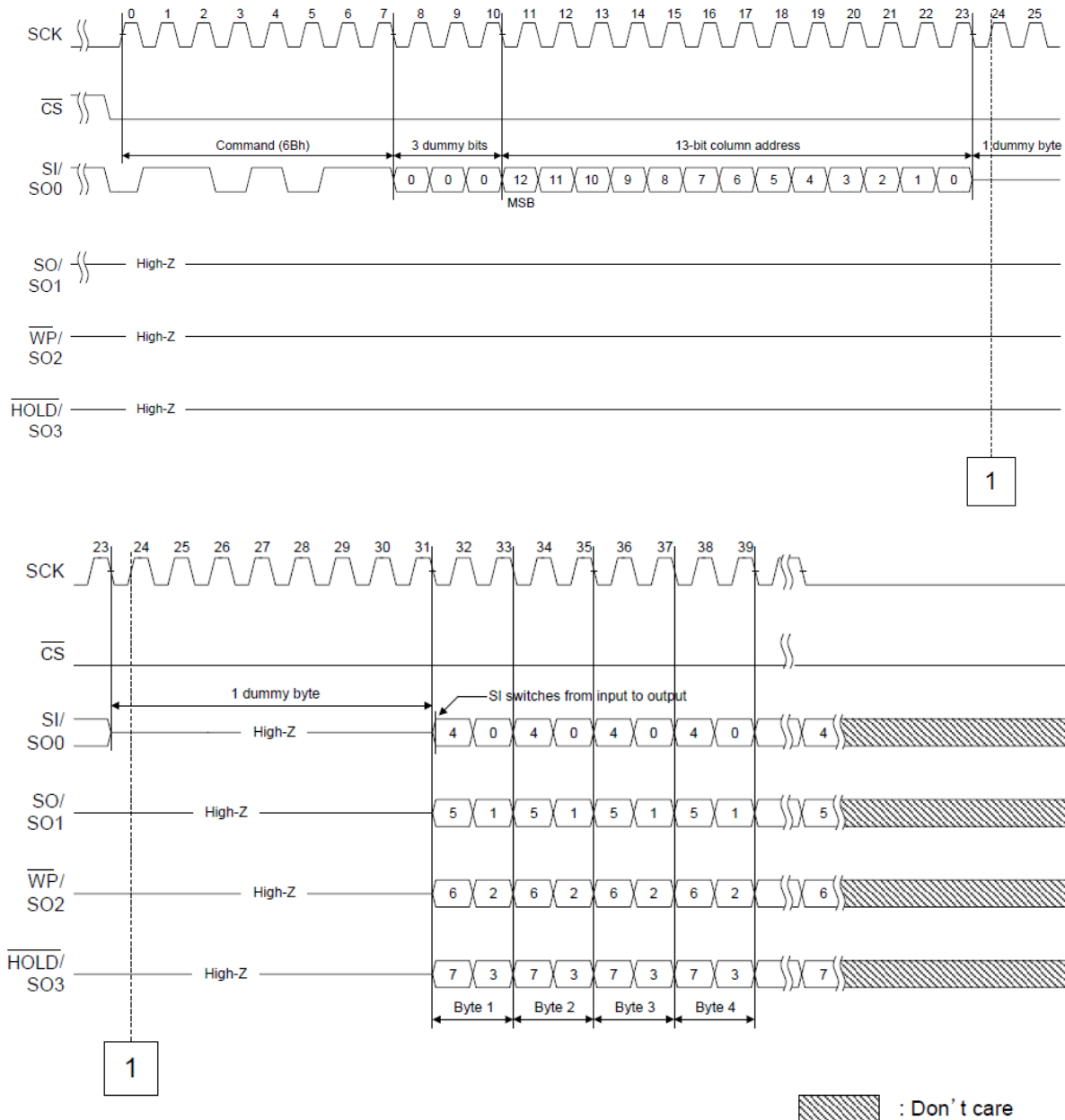


Figure 14. Page Read from Buffer x4 Timing

4.3. Page Read Operation - High Speed Mode

The device has a high speed mode for sequential read operation. When high speed mode is enabled, the average t_R is shortened. The command sequence is the same as the Page Read Operation. The users set or clear the HSE bit which enables or disables the high speed mode in the feature table as shown in Table 12. High speed mode is enabled (HSE bit is set to 1) in the default condition. When the users switch the HSE bit, users have to issue the Set Feature command just before the Read Cell Array (13h) command.

When the users use the random page read, the recommended setting of the HSE bit is 0 (disable).

4.4. Page Program Operation

The Program Load and Program Execute commands are required to program data to a page. The Program Load command transfers data to the buffer. The unit of data transfer is a byte. The Program Execute command programs data from the buffer to the cell array. The operation sequence is as follows.

1. Write Enable (06h) : To enable the Program Operation.
2. Program Load (02h) : To transfer data to the internal data buffer.
3. Program Execute (10h) : To program data from the buffer to the cell array.
4. Get Feature (0Fh) : To read the status of the device.

The internal data buffer is cleared by the Program Load command.

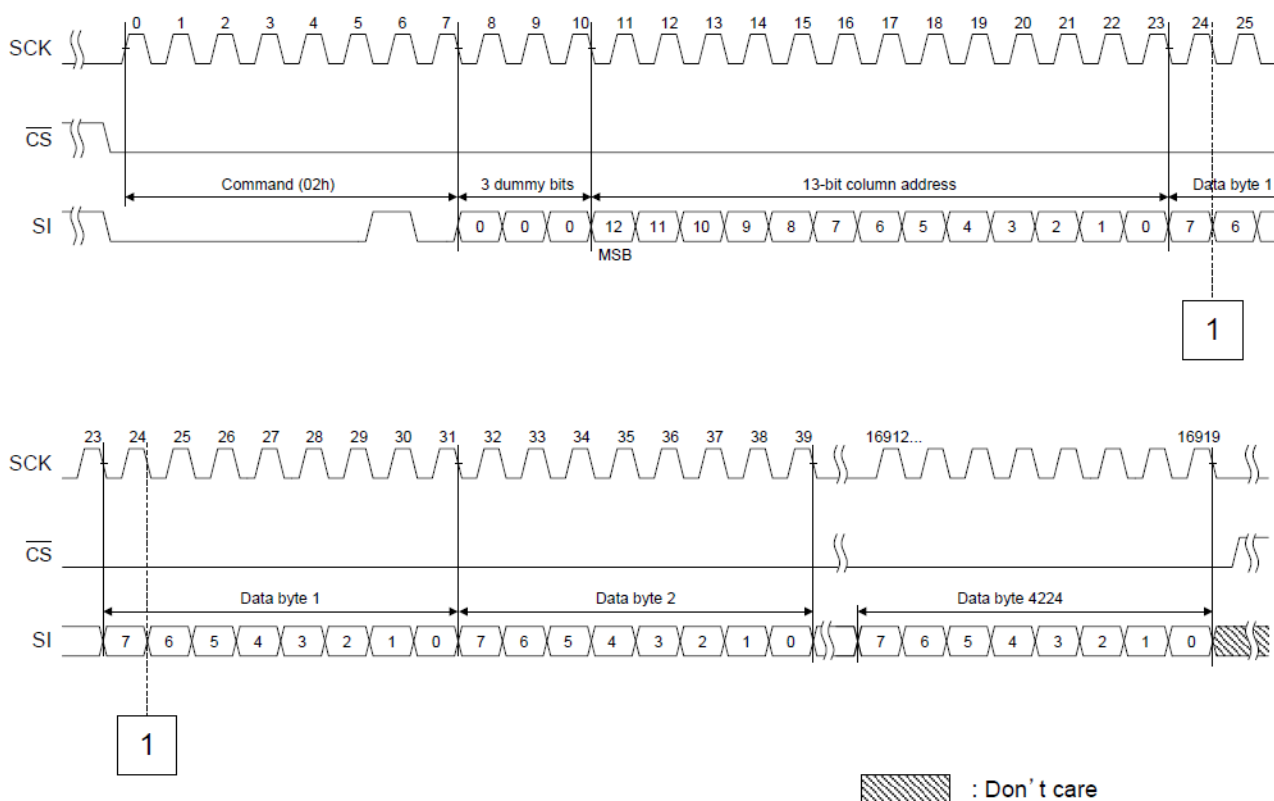
The Program Load Random Data (84h) command is also available to transfer data to the internal buffer. The users issue Program Load Random Data and the column address before the program execute (10h). The operation sequence is as follows.

1. Write Enable (06h) : To enable the Program Operation.
2. Program Load (02h) : To transfer data to the internal data buffer.
3. Program Load Random Data (84h) : To transfer data to the internal data buffer.
4. Program Execute (10h) : To program data from the buffer to the cell array.
5. Get Feature (0Fh) : To read the status of the device.

Program Load Random Data command is repeatable command.

The internal data buffer is not cleared by the Program Load Random Data command.

4.4.1. Program Load (02h)



Note:

When internal ECC is turned OFF, the maximum input data size is 4352 Bytes.

Figure 15. Program Load

4.4.2. Program Execute (10h)

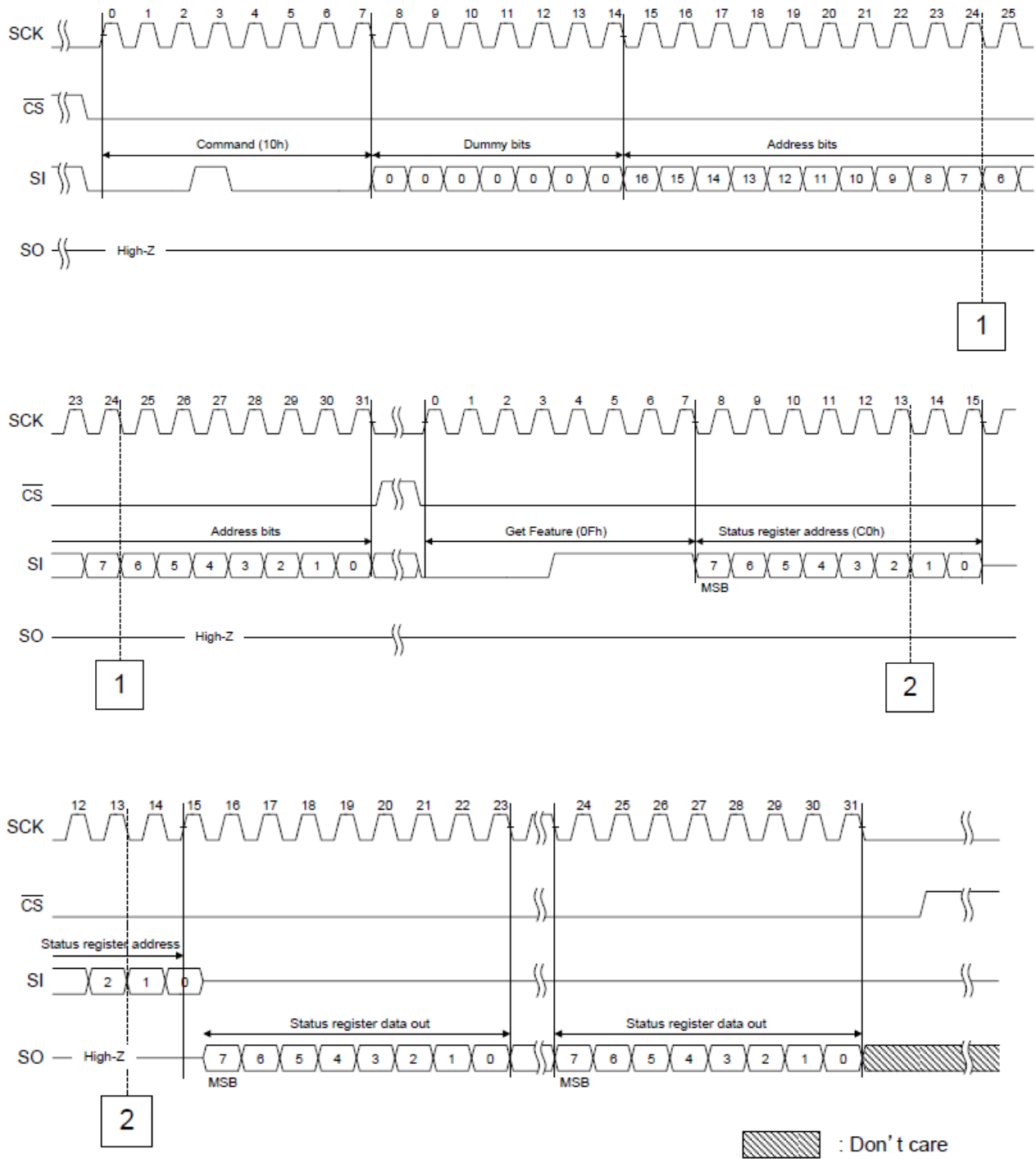
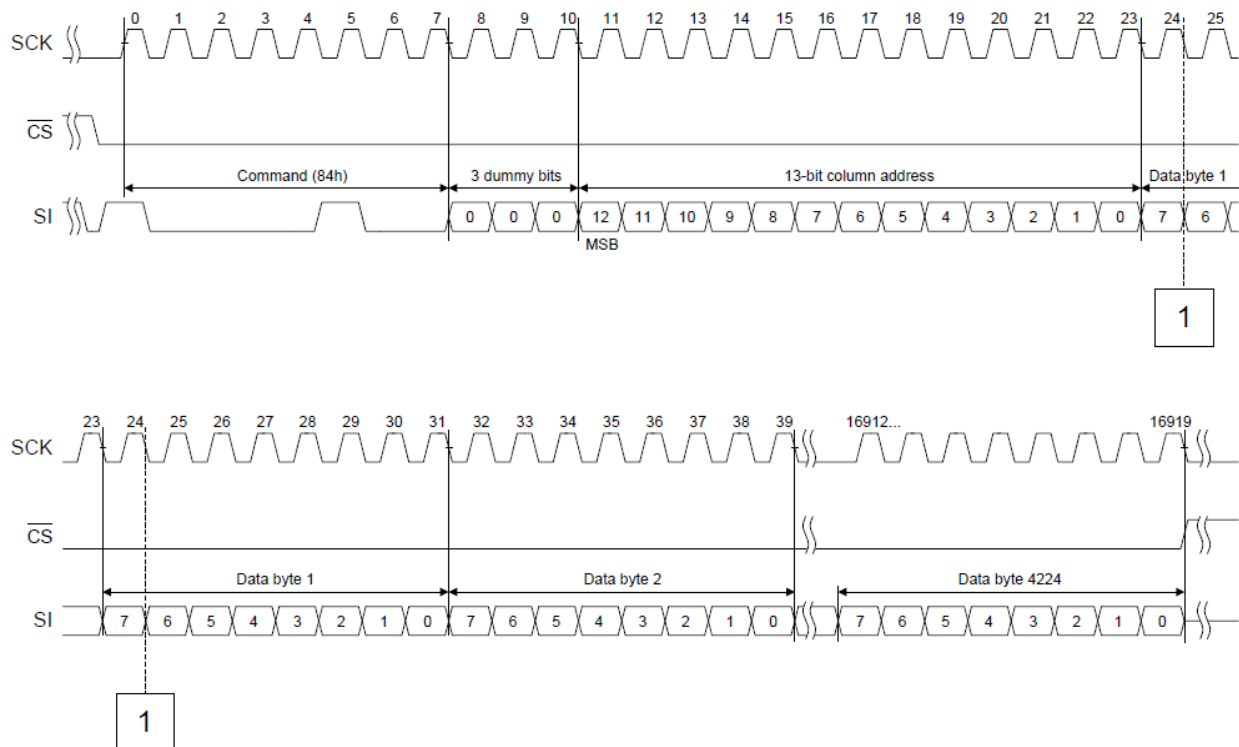


Figure 16. Program Execute Timing

4.4.3. Program Load Random Data (84h)



Note:

When internal ECC is turned OFF, the maximum input data size is 4352 Bytes.

Figure 17. Program Load Random Data Timing

4.5. Internal Data Move Operation

The Internal Data Move Operation is used to change the data in a page without data output. Before using this operation, the users must disable the Page Read High Speed Mode. The operation sequence is as follows.

1. Set Feature (1Fh) : To disable Page Read High Speed Mode.
2. Read Cell Array (13h) : To read data from the cell array to internal buffer.
3. Get Feature (0Fh) : To read the status of the device.
4. Write Enable (06h) : To enable the write.
5. Program Load Random Data (84h) : To change the data in the internal buffer.
6. Program Execute (10h) : To program data from the buffer to the cell array.
7. Get Feature (0Fh) : To read the status of the device.

Program Load Random Data command is repeatable command.

The status of the internal ECC depends on ECC_E bit in the feature table.

4.6. Block Erase (D8h)

The Block Erase Operation erases the selected block. The page address is ignored automatically.

The operation sequence is as follows.

1. Write Enable (06h) : To enable the Erase Operation.
2. Block Erase (D8h) : To erase data in the block.
3. Get Feature (0Fh) : To read the status of the device.

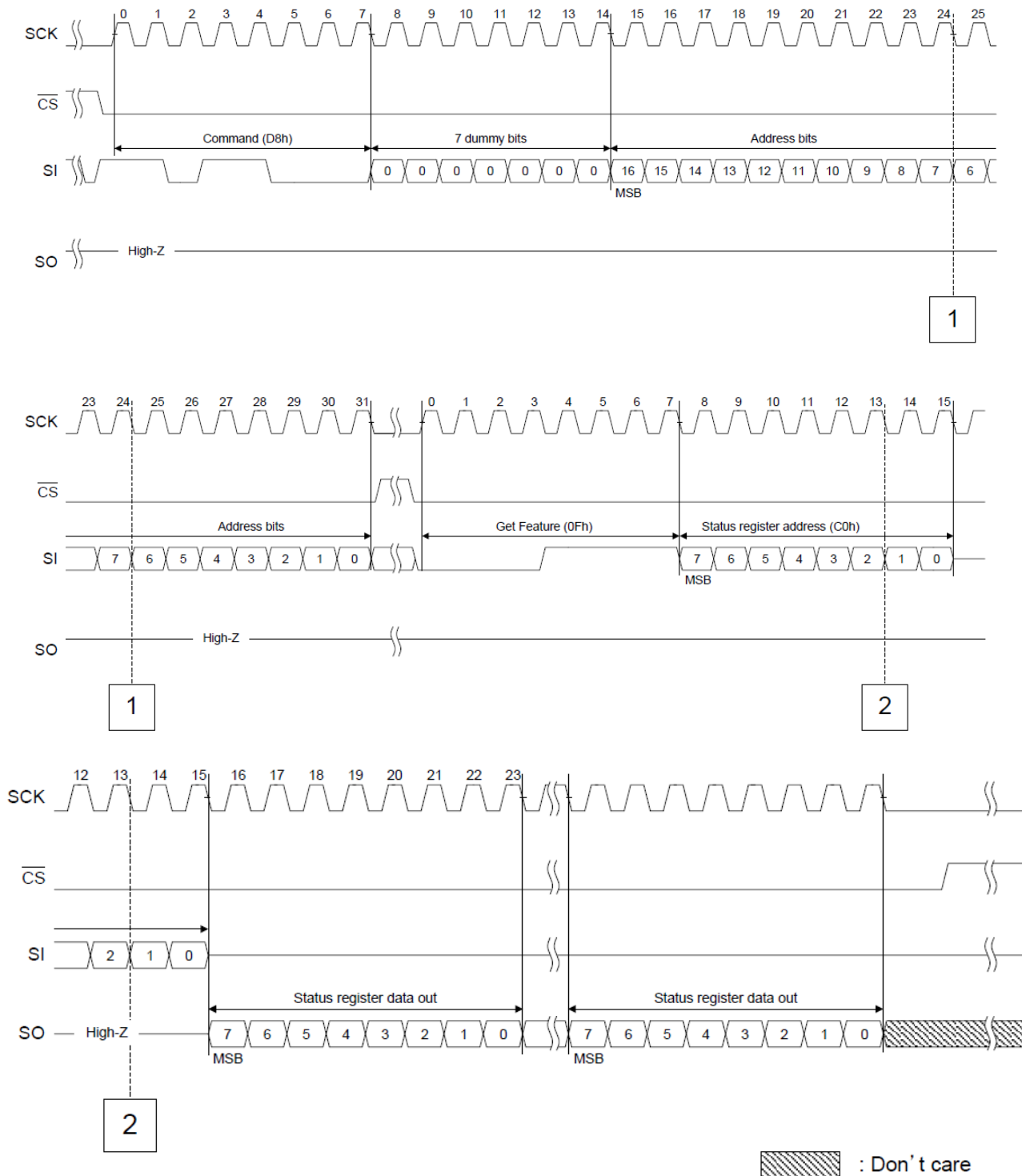


Figure 18. Block Erase Timing

4.7. Reset (FFh or FEh)

The Reset Operation stops all operations. For example, in case of a Program or Erase operation, the internally generated voltage is discharged to 0 volt and the device enters the busy state. The operation sequence is as follows.

1. Reset (FFh or FEh) :To reset the device
2. Get Feature (0Fh) :To read the status of the device

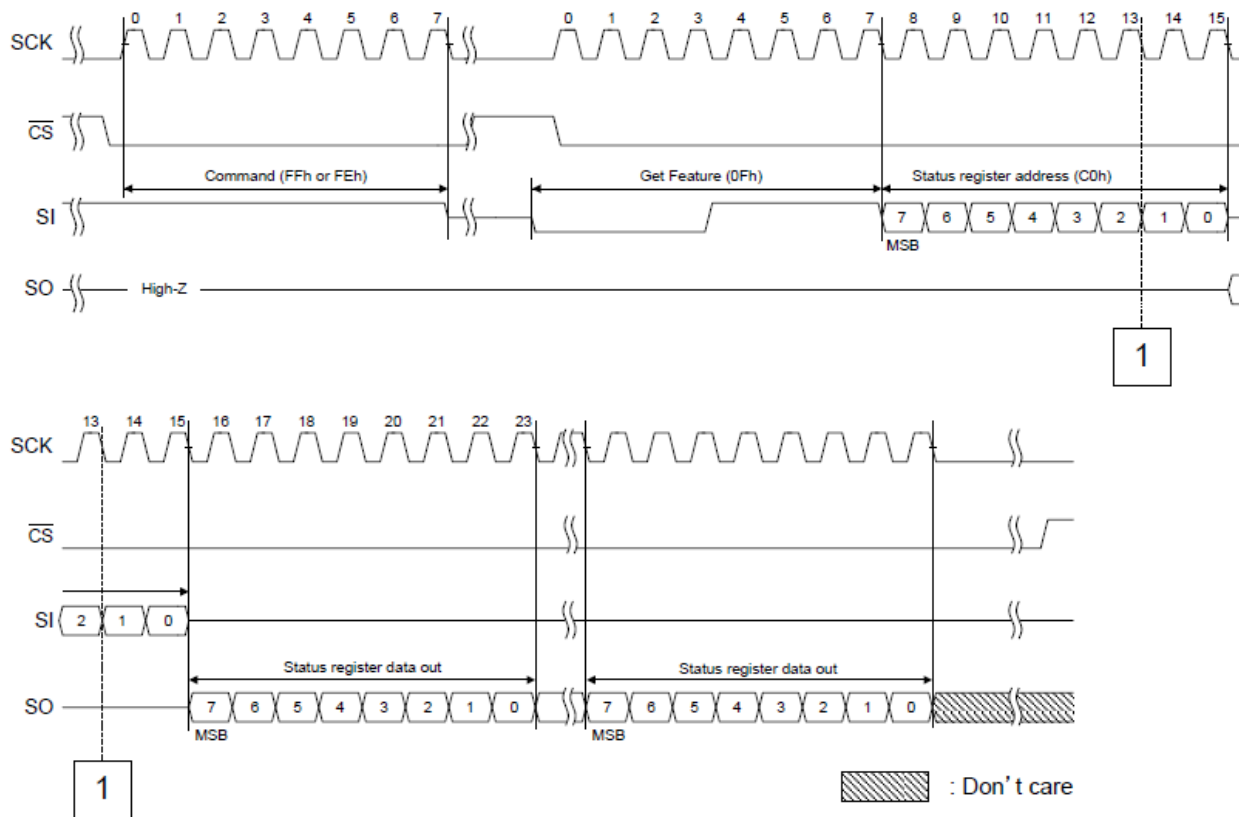


Figure 19. Reset Timing

4.8. Write Enable (06h) / Write Disable (04h)

The Write Enable / Disable commands set or reset the WEL (-Write Enable Latch) bit in the feature table shown in Table 12.

The Write Enable command sets the WEL bit to 1. The Write Enable command must be issued before the Page Program, Block Protection and Block Erase operations. The Write Disable command clears the WEL bit to 0. If the WEL bit is cleared, Page Program, Block Protection and Block Erase commands are ignored by the device.

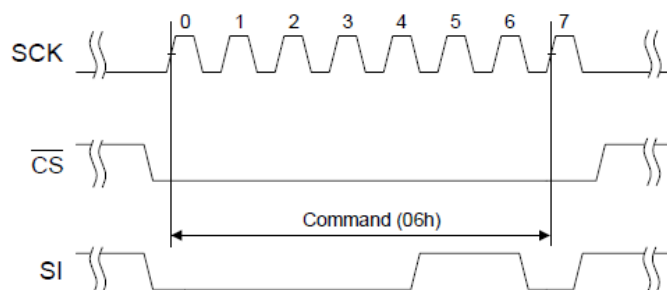


Figure 20. Write Enable

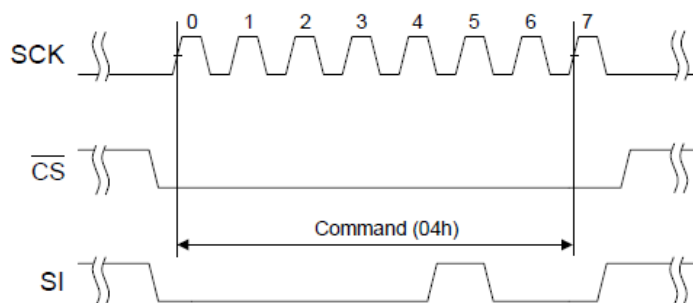


Figure 21. Write Disable Timing

4.9. Set Feature (1Fh) / Get Feature (0Fh)

The users set individual features using the Set Feature Operation and get feature settings or status of the device using the Get Feature Operation. Feature settings and status are shown in Table 12. Refer to other sections for the details of each setting and status. When a feature is set once by Set Feature command, the device keeps the bit until power OFF even if a reset (FFh or FEh) command is issued.

Table 12 Feature Table

Address	Bit							
	7	6	5	4	3	2	1	0
A0h	BRWD (R/W)	Reserved	BL2 (R/W)	BL1 (R/W)	BL0 (R/W)	Reserved	Reserved	Reserved
B0h	PRT_E (R/W)	IDR_E (R/W)	Reserved	ECC_E (R/W)	Reserved	BBI (R)	HSE (R/W)	Reserved
C0h	Reserved	Reserved	ECCS1 (R)	ECCS0 (R)	PRG_F (R)	ERS_F (R)	WEL (R/W)	OIP (R)
10h	BFD3 (R/W)	BFD2 (R/W)	BFD1 (R/W)	BFD0 (R/W)	Reserved	Reserved	Reserved	Reserved
20h	BFS7 (R)	BFS6 (R)	BFS5 (R)	BFS4 (R)	BFS3 (R)	BFS2 (R)	BFS1 (R)	BFS0 (R)
30h	MBF3 (R)	MBF2 (R)	MBF1 (R)	MBF0 (R)	Reserved	MFS2 (R)	MFS1 (R)	MFS0 (R)
40h	BFR7 (R)	BFR6 (R)	BFR5 (R)	BFR4 (R)	BFR3 (R)	BFR2 (R)	BFR1 (R)	BFR0 (R)
50h	BFR15 (R)	BFR14 (R)	BFR13 (R)	BFR12 (R)	BFR11 (R)	BFR10 (R)	BFR9 (R)	BFR8 (R)
60h	BFR23 (R)	BFR22 (R)	BFR21 (R)	BFR20 (R)	BFR19 (R)	BFR18 (R)	BFR17 (R)	BFR16 (R)
70h	BFR31 (R)	BFR30 (R)	BFR29 (R)	BFR28 (R)	BFR27 (R)	BFR26 (R)	BFR25 (R)	BFR24 (R)

Note:

(R/W) : Read / Write, (R): Read only

The users must use the Write Enable (06h) or the Write Disable (04h) command to switch the WEL bit.

Table 13 Feature Table - A0h Address Description

Bit	Symbol	Parameter	Read / Write	Description
7	BRWD	Block Register Write Disable	R/W	When WP pin is Low and BRWD is set to 1, over write for BRWD and BL bits are prohibit. 1b: Disable 0b: Enable (Default)
6	Reserved	-	-	Reserved
5	BL2	Block Lock 2	R/W	The users set the locked blocks as entire of device or portion of device using the BL bits. 000b: All Unlocked 001b: Upper 1/64 Locked 010b: Upper 1/32 Locked 011b: Upper 1/16 Locked 100b: Upper 1/8 Locked 101b: Upper 1/4 Locked 110b: Upper 1/2 Locked 111b: All Locked (Default)
4	BL1	Block Lock 1	R/W	
3	BL0	Block Lock 0	R/W	
2	Reserved	-	-	
1	Reserved	-	-	Reserved
0	Reserved	-	-	Reserved

Note:

(R/W) : Read / Write, (R): Read only

Refer to the description of BRWD and BL2-0 in 4.10 Block Lock Operation.

Table 14 Feature Table - B0h Address Description

Bit	Symbol	Parameter	Read / Write	Description
7	PRT_E	Block Protect Enable	R/W	The setting for Block Protection. 0b: Normal Operation (Default) 1b: Block Protection Enable – The protect execute command (2Ah) is acceptable for block protection.
6	IDR_E	ID Read Enable	R/W	The setting for Parameter Page Read and Unique ID Read. 0b: Normal Operation (Default) 1b: Parameter Page Read and Unique ID read mode
5	Reserved	-	-	Reserved
4	ECC_E	ECC Enable	R/W	The setting for internal ECC Function. 0b: Internal ECC Disable 1b: Internal ECC Enable (Default)
3	Reserved	-	-	Reserved
2	BBI	Bad Block Inhibit	R	The setting for Bad Block Inhibit Function. 0b: Not Available 1b: Bad Block Inhibit Enable (Default)
1	HSE	High Speed Mode Enable	R/W	The setting for Page Read High Speed Mode. 0b: High Speed Mode Disable 1b: High Speed Mode Enable (Default)
0	Reserved	-	-	Reserved

Note:

(R/W) : Read / Write, (R): Read only

Refer to the description of PRT_E in 4.10

Refer to the description of ECC_E in 4.16.1 ECC Switch.

Refer to the description of BBI in 4.15 Bad Block Inhibit.

Refer to the description of HSE in 4.3 Page Read Operation - High Speed Mode.

Table 15 Feature Table - C0h Address Description

Bit	Symbol	Parameter	Read / Write	Description
7	Reserved	-	-	Reserved
6	Reserved	-	-	Reserved
5	ECES1	ECC Status 1	R	ECC status bits indicate the status of internal ECC operation. 00b: No bit flips were detected in previous page read. 01b: Bit flips were detected and corrected. Bit flip count did not exceed the bit flip detection threshold. The threshold is set by bits [7:4] in address 10h in the feature table. 10b: Multiple bit flips were detected and not corrected. 11b: Bit flips were detected and corrected. Bit flip count exceeded the bit flip detection threshold. The threshold is set by bits [7:4] in address 10h in the feature table.
4	ECES0	ECC Status 0	R	
3	PRG_F	Program Fail	R	Program fail bit indicates that a program failure has occurred in the previous Program Operation. 0b: Program Pass 1b: Program Fail
2	ERS_F	Erase Fail	R	Erase fail bit indicates that an erase failure has occurred in the previous Erase Operation. 0b: Erase Pass 1b: Erase Fail
1	WEL	Write Enable Latch	R/W	This bit indicates the status of write enable/disable. 0b: Write Disable (Default) 1b: Write Enable
0	OIP	Operation In Progress	R	This bit indicates the status of the device. This bit will be set while busy state. 0b: Operation is not in progress. Ready state. 1b: Operation is in progress. Busy state.

Note:

(R/W) : Read / Write, (R): Read only

The users must use the Write Enable (06h) or the Write Disable (04h) command to switch the WEL bit.

Once the Get Feature command is issued, the status and setting information are outputted continuously.

OIP bit is updated automatically during the status information are outputted continuously.

4.9.1. Set Feature (1Fh)

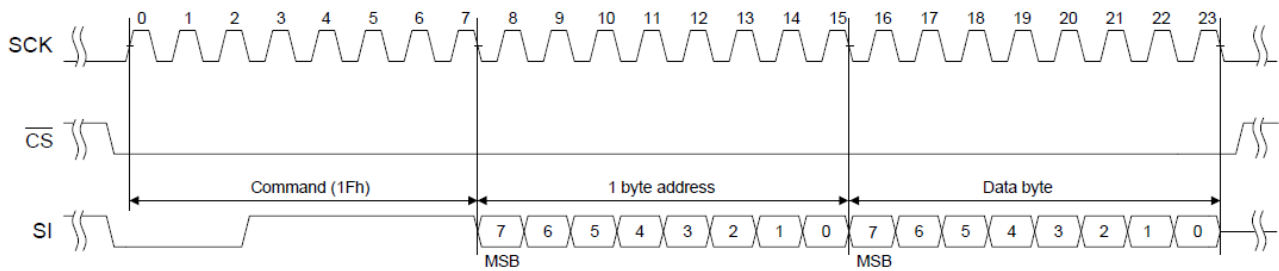


Figure 22. Set Feature Timing

4.9.2. Get Feature (0Fh)

After the Get Feature command and the address are inputted, the 8bit status and setting information will be outputted continuously until CS goes High.

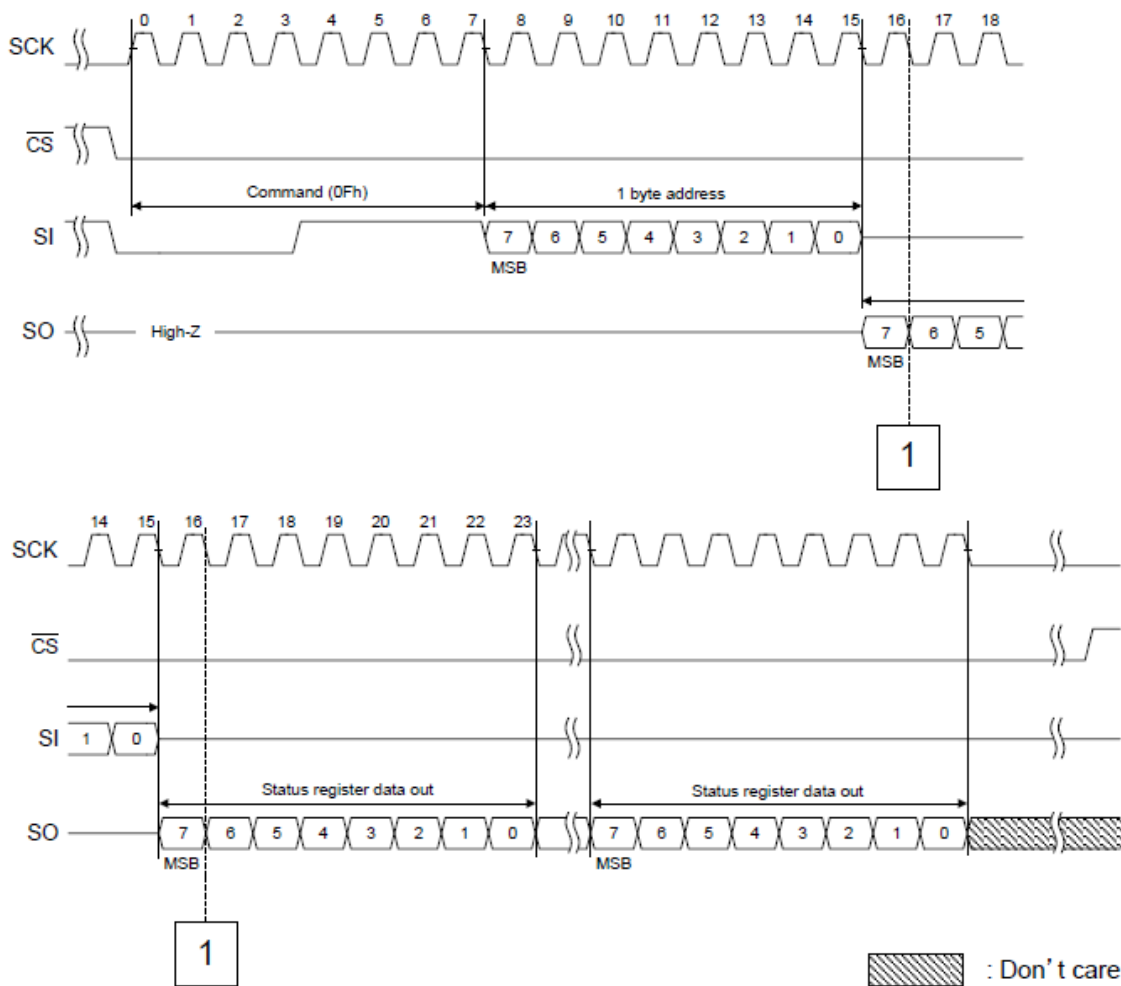


Figure 23. Get Feature Timing

4.10. Block Lock Operation

The Block Lock Operation locks blocks and prevents Program and Erase operations. The users set the range of locked blocks as the entire device or a portion of the device using the BL bits (bits [5:3]) in address A0h of the feature table shown in Table 12. The users set the BL bits by the Set Feature Operation. After the power on sequence, all blocks are locked (bits [5:3] are all set to 1). If the Program Execute (10h) or Block Erase (D8h) commands are issued to locked blocks, Program Fail or Erase Fail will be indicated in the feature table shown in Table 12.

The users must clear / change the BL bits using Set Feature command to unlock the entire of the device or portion of the device. When BRWD bit is set and WP pin is Low, the users cannot switch the BRWD and the BL bits.

The Block Lock Operation is different from the Block Protection Operation.

Table 16 Block Lock Setting

BL2	BL1	BL0	Protect Area
0	0	0	All Unlocked
0	0	1	Upper 1/64 Locked
0	1	0	Upper 1/32 Locked
0	1	1	Upper 1/16 Locked
1	0	0	Upper 1/8 Locked
1	0	1	Upper 1/4 Locked
1	1	0	Upper 1/2 Locked
1	1	1	All Locked

4.11. Block Protection Operation (One Time Program)

The Block Protection Operation provides the function to prohibit the Program and Erase operations to user selected blocks. The users protect individual blocks using the Set Feature, Write Enable and Protect Execute commands. The last 128 blocks of the device are able to be set to protected blocks. The block protection setting is permanent. Once a block is protected, the user cannot unprotect the block.

When PRT_E (bit [7]) in address B0h of the feature table is set to 1, and the users issue the Protect Execute command (2Ah), the user block will become a protected block. The users must set the PRT_E bit (bit [7]) just before the Write Enable command for the Protect Execute. After the protection to the block, the users must clear bit [7] in address B0h using the Set Feature command. The users can issue the Protect Execute (2Ah) only one time for each block.

The Block Protection Operation is different from the Block Lock Operation.

The operation sequence to set block “N” as a protected block is as follows.

1. Set Feature (1Fh) : To set PRT_E bit [7] in address B0h to block protection mode.
2. Write Enable (06h) : To enable the protect execute command.
3. Protect Execute (2Ah) for block “N” : To protect the block “N”.
4. Get Feature (0Fh) : To read the status of the device.
5. Set Feature (1Fh) : To clear PRT_E bit [7] in address B0h.

Table 17 Block Protection Setting

PRT_E	State
0	Normal Operation (Default)
1	Block Protection Enable – The Protect Execute command (2Ah) is acceptable for block protection.

Table 18 Block Number for Block Protection

Block Number	Block Protection
Block 0 – Block 1919	The users cannot protect these blocks by block protection operation.
Block 1920 – Block 2047	The users can protect these blocks by block protection operation.

4.11.1. Protect Execute (2Ah)

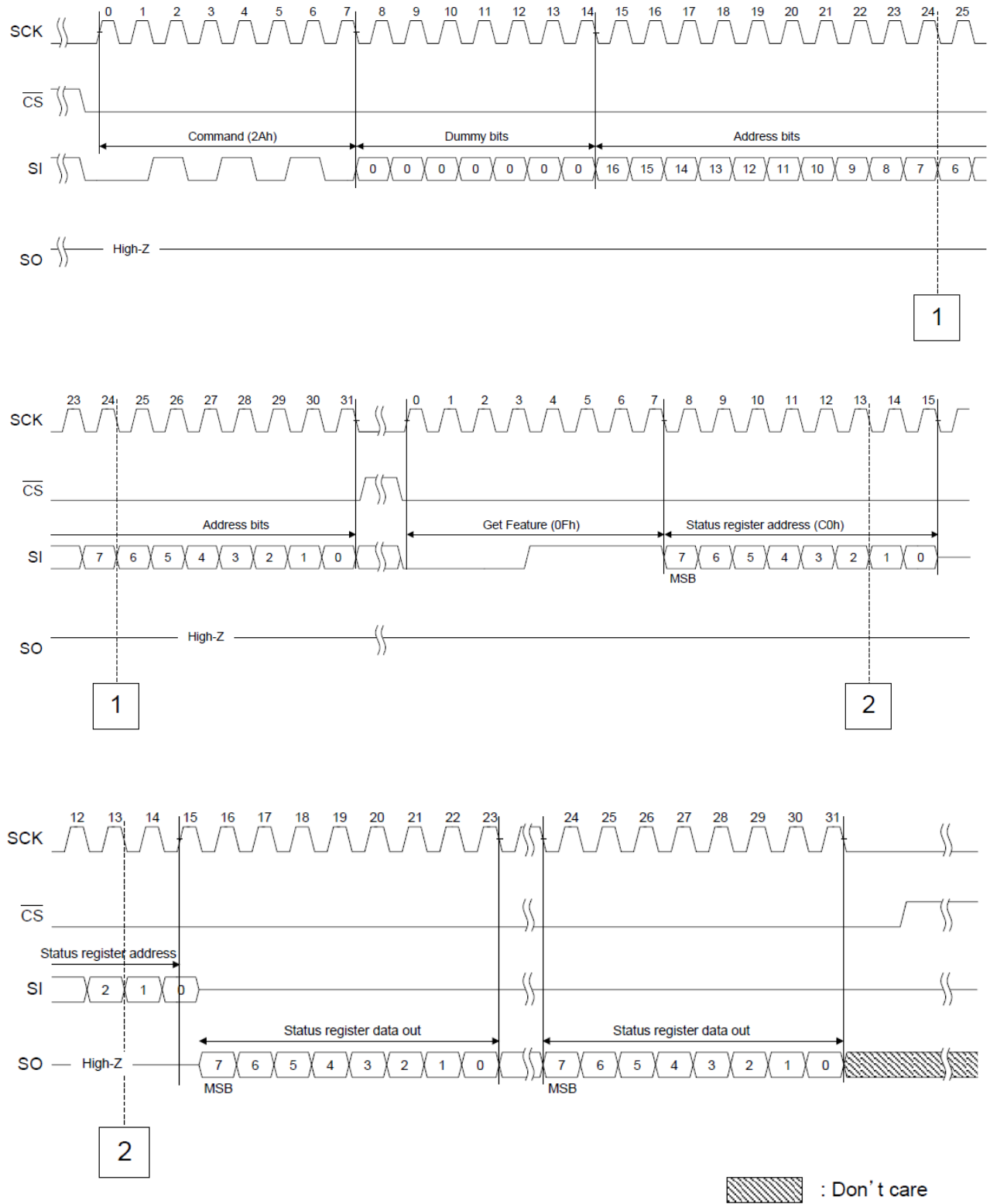


Figure 24. Protect Execute Timing

4.12. Parameter Page Read Operation

The device has a parameter page. The operation sequence is as follows.

1. Set Feature (1Fh) with address B0h and set bit [6]. : To set the IDR_E bit in the feature table.
2. Read Cell Array (13h) with address 01h. : To read the parameter page.
3. Get Feature (0Fh) : To read the status of the device.
4. Read Buffer (03h or 0Bh) with address 00h. : To output the parameter page.
or Read Buffer x2 (3Bh)
or Read Buffer x4 (6Bh)
5. Set Feature (1Fh) with address B0h and clear bit [6]. : To clear the IDR_E bit in the feature table.

Table 19 Parameter Page

Byte	Parameter		Value
0 - 3	Signature		4Eh, 41h, 4Eh, 44h
4 - 31	Reserved		All 00h
32 - 43	Device manufacturer		54h, 4Fh, 53h, 48h, 49h, 42h, 41h, 20h, 20h, 20h, 20h, 20h
44 - 63	Device model	TC58CVG2S0HRAIG (WSON8)	54h, 43h, 35h, 38h, 43h, 56h, 47h, 32h, 53h, 30h, 48h, 52h, 41h, 49h, 47h, 20h, 20h, 20h, 20h, 20h
64	Manufacturer ID		98h
65 - 79	Reserved		All 00h
80 - 83	Number of data bytes per page		00h, 10h, 00h, 00h
84 - 85	Number of spare bytes per page		80h, 00h
86 - 89	Number of data bytes per partial page		00h, 02h, 00h, 00h
90 - 91	Number of spare bytes per partial page		10h, 00h
92 - 95	Number of pages per block		40h, 00h, 00h, 00h
96 - 99	Number of blocks per unit		00h, 08h, 00h, 00h
100	Number of logical units		01h
101	Number of address cycles		00h
102	Number of bits per cell		01h
103 - 104	Bad blocks maximum per unit		28h, 00h
105 - 106	Block endurance		01h, 05h
107	Guaranteed valid blocks at beginning of target		01h
108 - 109	Reserved		All 00h
110	Number of programs per page		04h
111	Reserved		00h
112	Number of ECC bits		00h
113 - 127	Reserved		All 00h
128	I/O pin capacitance		04h
129 - 132	Reserved		All 00h
133 - 134	tPROG maximum page program time		58h, 02h
135 - 136	tBERS maximum block erase time		58h, 1Bh
137 - 138	tR maximum page read time		18h, 01h
139 - 253	Reserved		All 00h
254 - 255	Integrity CRC	TC58CVG2S0HRAIG (WSON8)	F5h, E1h
256 - 511	Value of bytes 0-255		-
512 - 767	Value of bytes 0-255		-

Note:

The value of all parameters are default setting of the device.

When the users change the setting of the device such as internal ECC enable/disable, parameter page is not updated.

4.13. Read ID (9Fh)

The ID of the device is read by command 9Fh.

Table 20 ID Table

Byte	Description	Value
Byte 0	Manufacture ID (Toshiba)	98h
Byte 1	Device ID	CDh

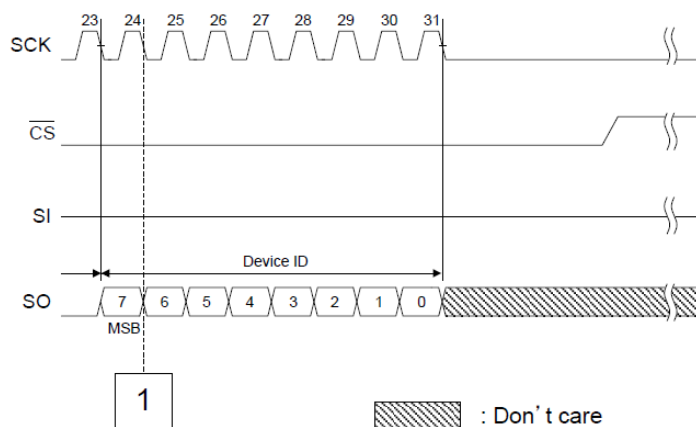
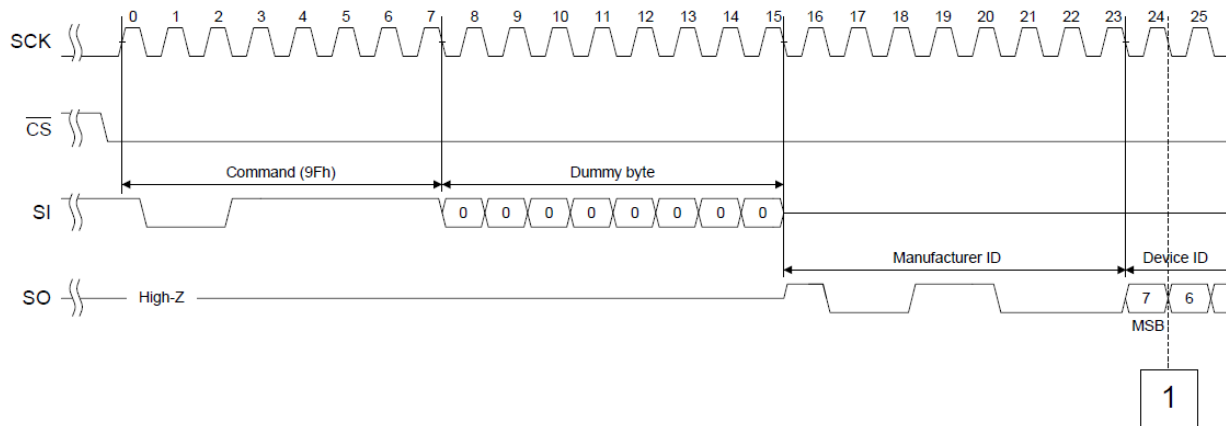


Figure 25. Read ID Timing

4.14. Unique ID Read Operation

The device has a unique ID and it is different for each device. The device has 16 copies of 32 bytes of unique ID data. The first 16 bytes of data are unique ID data and the second 16 bytes of data are the complement value of the first 16 bytes of data. The operation sequence is as follows.

1. Set Feature (1Fh) with address B0h and set bit [6]. : To set the IDR_E bit in the feature table.
2. Read Cell Array (13h) with address 00h. : To read the unique ID.
3. Get Feature (0Fh) : To read the status of the device.
4. Read Buffer (03h or 0Bh) with address 00h. : To output the 16 copies of the Unique ID.
or Read Buffer x2 (3Bh)
or Read Buffer x4 (6Bh)
5. Set Feature (1Fh) with address B0h and clear bit [6]. : To clear the IDR_E bit in the feature table.

4.15. Bad Block Inhibit

The device occasionally contains unusable blocks in its initial condition. The page program operation and erase operation are prohibited to invalid blocks. The device has a bad block inhibit function to protect initial invalid blocks. When the users issue the program or erase command to the initial invalid blocks, the device ignores these commands automatically and program fail or erase fail is indicated in the feature table as shown in Table 12. The bad block inhibit function is enabled by default and this setting is permanent.

4.16. Internal ECC

The device has internal ECC and it generates error correction code during the busy time in a Program Operation. The ECC logic manages 9bit error detection and 8bit error correction in each 528 bytes of main data and spare data. A section of the main area (512 bytes) and spare area (16 bytes) are paired for ECC calculation. During the Read Operation, the device executes ECC by itself. Once the Read command is executed, the Get Feature command can be issued to check the read status. The read status remains until other valid commands are executed.

The device has the functions of bit flip detection and maximum bit flip count report. Internal ECC detects the bit flips in each sector and the maximum bit flip count in a page. These results are indicated in the feature table as shown in Table 12.

Table 21 Page Assignment

1st Main	2nd Main	3rd Main	4th Main	5th Main	6th Main	7th Main	8th Main	1st Spare	2nd Spare	3rd Spare	4th Spare	5th Spare	6th Spare	7th Spare	8th Spare
512B	512B	512B	512B	512B	512B	512B	512B	16B	16B	16B	16B	16B	16B	16B	16B

Table 22 Definition of 528 bytes Data Pair

Data Pair	Column Address	
	Main Area	Spare Area
1st Data Pair	0 - 511	4096 - 4111
2nd Data Pair	512 - 1023	4112 - 4127
3rd Data Pair	1024 - 1535	4128 - 4143
4th Data Pair	1536 - 2047	4144 - 4159
5th Data Pair	2048 - 2559	4160 - 4175
6th Data Pair	2560 - 3071	4176 - 4191
7th Data Pair	3072 - 3583	4192 - 4207
8th Data Pair	3584 - 4095	4208 - 4223

Note:

The users cannot access to column addresses 4224 – 4351 if internal ECC is enabled.

While using the Partial Page Program, the users must program the data to main area and spare area simultaneously by the definition of data pair.

4.16.1. ECC Switch

The internal ECC is enabled after the power on sequence. The users switch the ECC_E bit (bit [4]) in address B0h of the feature table to enable or disable the internal ECC. The users set or clear a bit by the Set Feature command. If the ECC_E bit is cleared to 0 in the feature table, internal ECC will be disabled. In this case, the spare area size is changed from 128 bytes to 256 bytes automatically. When the users switch the ECC_E bit, the users must issue the Set Feature command just before the Read Cell Array (13h) command.

4.16.2. ECC Status

The ECC Status function is used to monitor the error correction status. The device can correct up to 8bit errors. ECC is performed on the NAND Flash main and spare areas. The ECC status is indicated in the ECCS1 and ECCS0 bit (bits [5:4]) in address C0h of the feature table shown in Table 15. The users issue the Get Feature command to read the ECC status.

4.16.3. ECC Bit Flip Count Detection

The ECC Bit Flip Count Detection function detects the bit flip count in a page. The users set the threshold bit count using the Set Feature command. The threshold bit count is decided by the bit flip detection setting bit (BFD) in address 10h in the feature table as shown in Table 12. The detected results will be indicated in the BFS bits (bits [7:0]) in address 20h. When bit flips exceed the threshold in a sector, the BFS bits are set after the Read Buffer command.

Table 23 Bit Flip Count Detection Setting (BFD)

BFD3	BFD2	BFD1	BFD0	Description
0	0	0	0	Reserved
0	0	0	1	Detect a bit flip in a sector.
0	0	1	0	Detect 2 bit flips in a sector.
0	0	1	1	Detect 3 bit flips in a sector.
0	1	0	0	Detect 4 bit flips in a sector. (Default)
0	1	0	1	Detect 5 bit flips in a sector.
0	1	1	0	Detect 6 bit flips in a sector.
0	1	1	1	Detect 7 bit flips in a sector.
1	0	0	0	Detect 8 bit flips in a sector.
1	1	1	1	Detect the uncorrectable error (9+ bit errors in a sector).

Table 24 Bit Flip Count Detection Status (BFS) (Feature Table - 20h Address Description)

Bit	Symbol	Parameter	Read / Write	Description
7	BFS7	Bit Flip Count Detection Status 7	R	Bit flip count detection status 7 indicates that the bit flip count in sector 7 is more than threshold bit count. 0b: Bit flip count in sector 7 is less than the threshold. 1b: Bit flip count in sector 7 is the threshold bit count or more than the threshold bit count.
6	BFS6	Bit Flip Count Detection Status 6	R	Bit flip count detection status 6 indicates that the bit flip count in sector 6 is more than threshold bit count. 0b: Bit flip count in sector 6 is less than the threshold. 1b: Bit flip count in sector 6 is the threshold bit count or more than the threshold bit count.
5	BFS5	Bit Flip Count Detection Status 5	R	Bit flip count detection status 5 indicates that the bit flip count in sector 5 is more than threshold bit count. 0b: Bit flip count in sector 5 is less than the threshold. 1b: Bit flip count in sector 5 is the threshold bit count or more than the threshold bit count.
4	BFS4	Bit Flip Count Detection Status 4	R	Bit flip count detection status 4 indicates that the bit flip count in sector 4 is more than threshold bit count. 0b: Bit flip count in sector 4 is less than the threshold. 1b: Bit flip count in sector 4 is the threshold bit count or more than the threshold bit count.
3	BFS3	Bit Flip Count Detection Status 3	R	Bit flip count detection status 3 indicates that the bit flip count in sector 3 is more than threshold bit count. 0b: Bit flip count in sector 3 is less than the threshold. 1b: Bit flip count in sector 3 is the threshold bit count or more than the threshold bit count.
2	BFS2	Bit Flip Count Detection Status 2	R	Bit flip count detection status 2 indicates that the bit flip count in sector 2 is more than threshold bit count. 0b: Bit flip count in sector 2 is less than the threshold. 1b: Bit flip count in sector 2 is the threshold bit count or more than the threshold bit count.
1	BFS1	Bit Flip Count Detection Status 1	R	Bit flip count detection status 1 indicates that the bit flip count in sector 1 is more than threshold bit count. 0b: Bit flip count in sector 1 is less than the threshold. 1b: Bit flip count in sector 1 is the threshold bit count or more than the threshold bit count.
0	BFS0	Bit Flip Count Detection Status 0	R	Bit flip count detection status 0 indicates that the bit flip count in sector 0 is more than threshold bit count. 0b: Bit flip count in sector 0 is less than the threshold. 1b: Bit flip count in sector 0 is the threshold bit count or more than the threshold bit count.

4.16.4. ECC Bit Flip Count Report

The ECC Bit Flip Count Report function reports the bit flip count of each sector in a page. The users can read the bit flip count using the Get Feature command with address 40h, 50h, 60h and 70h.

Table 25 Bit Flip Count Report for Sector 0 (BFR)

BFR3	BFR2	BFR1	BFR0	Description
0	0	0	0	No bit flip occurred in sector 0.
0	0	0	1	A bit flip occurred in sector 0 and corrected.
0	0	1	0	2 bit flips occurred in sector 0 and corrected.
0	0	1	1	3 bit flips occurred in sector 0 and corrected.
0	1	0	0	4 bit flips occurred in sector 0 and corrected.
0	1	0	1	5 bit flips occurred in sector 0 and corrected.
0	1	1	0	6 bit flips occurred in sector 0 and corrected.
0	1	1	1	7 bit flips occurred in sector 0 and corrected.
1	0	0	0	8 bit flips occurred in sector 0 and corrected.
1	1	1	1	Bit flips over 8 bits occurred in sector 0 and were not corrected.

Table 26 Sector Definition (BFR)

BFR7	BFR6	BFR5	BFR4	BFR3	BFR2	BFR1	BFR0
Sector 1				Sector 0			
BFR15	BFR14	BFR13	BFR12	BFR11	BFR10	BFR9	BFR8
Sector 3				Sector 2			
BFR23	BFR22	BFR21	BFR20	BFR19	BFR18	BFR17	BFR16
Sector 5				Sector 4			
BFR31	BFR30	BFR29	BFR28	BFR27	BFR26	BFR25	BFR24
Sector 7				Sector 6			

4.16.5. ECC Maximum Bit Flip Count Report

The ECC Maximum Bit Flip Count Report function provides the maximum bit flip count in a page. The maximum count is indicated in address 30h of the feature table shown in Table 12. The sector number in which the maximum bit flip occurred in a page is indicated in the MFS bit (bits [2:0]) in address 30h as shown in Table 28. When several sector's maximum bit flip count are the same, the lowest sector number is indicated in these bits. The users get the report using the Get Feature command.

Table 27 Maximum Bit Flip Count (MBF)

MBF3	MBF2	MBF1	MBF0	Description
0	0	0	0	No bit error is detected in the page.
0	0	0	1	Maximum bit flip count is 1 bit in a sector. Bit flip was corrected.
0	0	1	0	Maximum bit flip count is 2 bits in a sector. Bit flips were corrected.
0	0	1	1	Maximum bit flip count is 3 bits in a sector. Bit flips were corrected.
0	1	0	0	Maximum bit flip count is 4 bits in a sector. Bit flips were corrected.
0	1	0	1	Maximum bit flip count is 5 bits in a sector. Bit flips were corrected.
0	1	1	0	Maximum bit flip count is 6 bits in a sector. Bit flips were corrected.
0	1	1	1	Maximum bit flip count is 7 bits in a sector. Bit flips were corrected.
1	0	0	0	Maximum bit flip count is 8 bits in a sector. Bit flips were corrected.
1	1	1	1	Maximum bit flip count exceed 8 bits in a sector. Bit flips were not corrected.

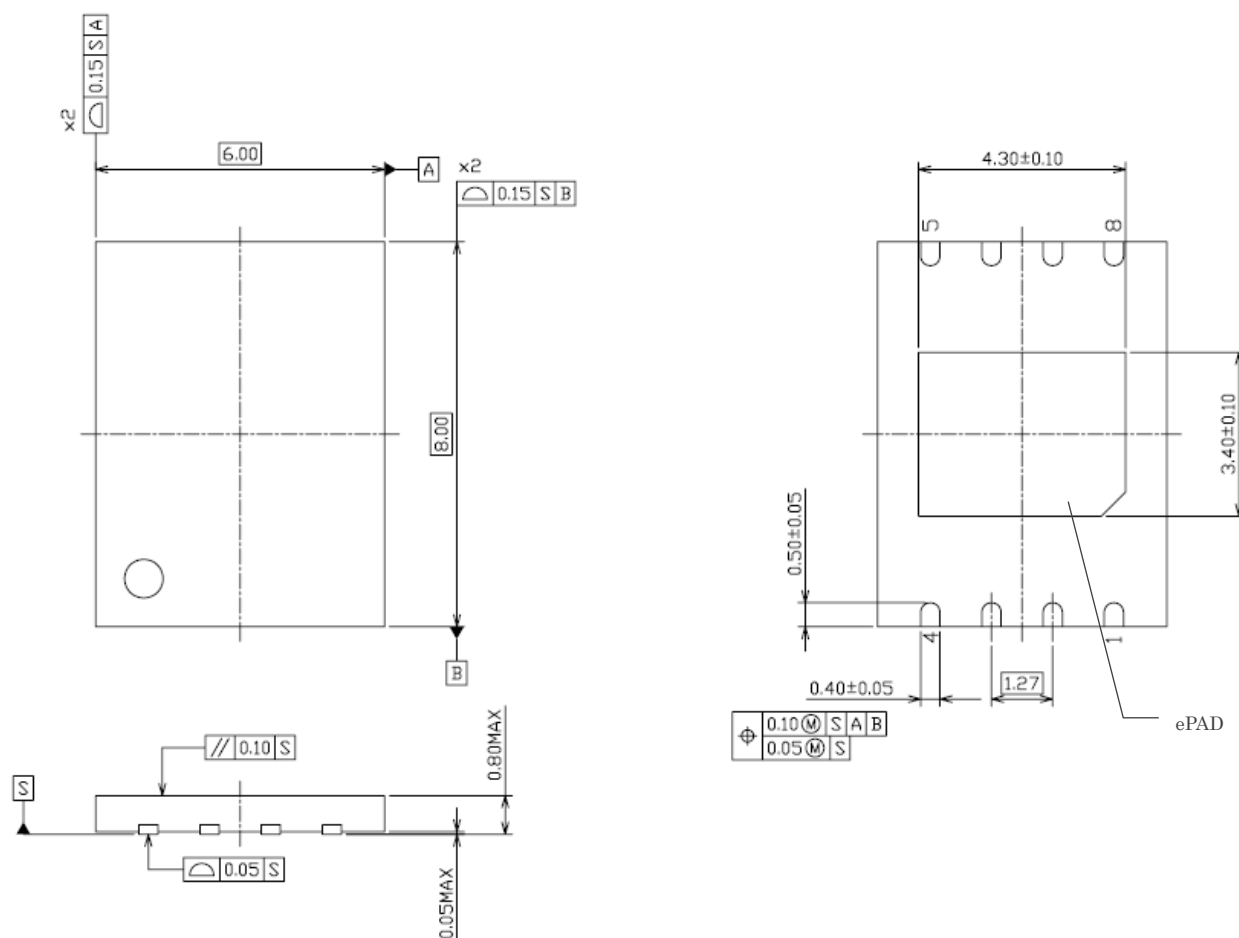
Table 28 Maximum Bit Flip Count Sector (MFS)

MFS2	MFS1	MFS0	Description
0	0	0	Maximum bit flips occurred in sector 0.
0	0	1	Maximum bit flips occurred in sector 1.
0	1	0	Maximum bit flips occurred in sector 2.
0	1	1	Maximum bit flips occurred in sector 3.
1	0	0	Maximum bit flips occurred in sector 4.
1	0	1	Maximum bit flips occurred in sector 5.
1	1	0	Maximum bit flips occurred in sector 6.
1	1	1	Maximum bit flips occurred in sector 7.

5. Package Information

5.1. WSON8

The WSON8 features a exposed PAD (ePAD). The ePAD is configured on the package bottom without any connection to the chip inside. It is recommended for users to solder the ePAD onto PC board with connection to VSS or None, as the adhesive strength to the PC board will be enhanced.



6. Application Notes

6.1. Prohibition of Unspecified Commands

The operation commands are listed in Table 11. Input of a command other than those specified in Table 11 is prohibited. Stored data may be corrupted if an unknown command is entered during the command cycle.

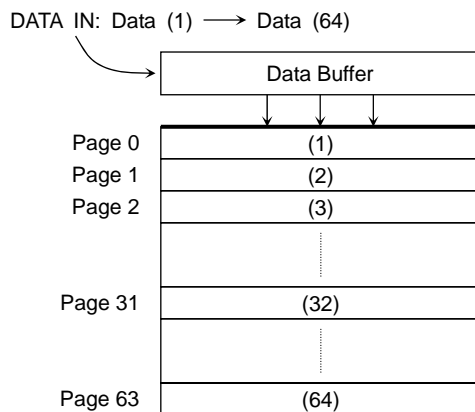
6.2. Restriction of Commands while in the Busy State

During the operation in progress, do not input any command except Get Feature(0Fh) and Reset(FFh or FEh).

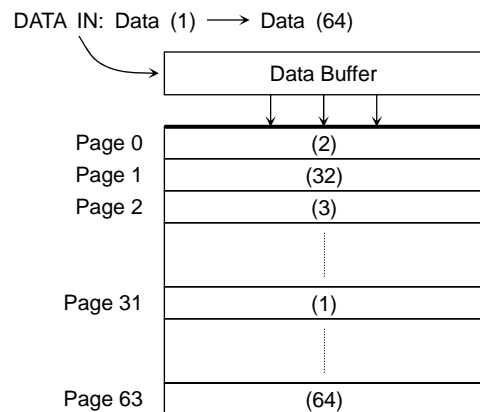
6.3. Addressing for Page Program Operation

Within a block, the pages must be programmed consecutively from the LSB (least significant bit) page of the block to MSB (most significant bit) page of the block. Random page address programming is prohibited.

From the LSB page to MSB page



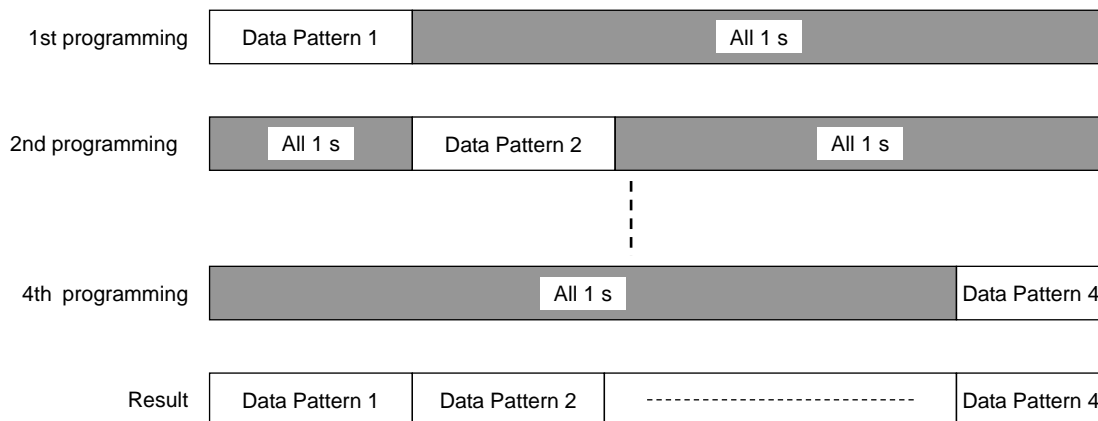
Ex.) Random page program (Prohibition)



6.4. Several programming Cycles on the Same Page (Partial Page Program)

Each segment can be programmed individually as follows:

Partial Page Program should follow the Table 22 restriction while ECC_E is set to 1.



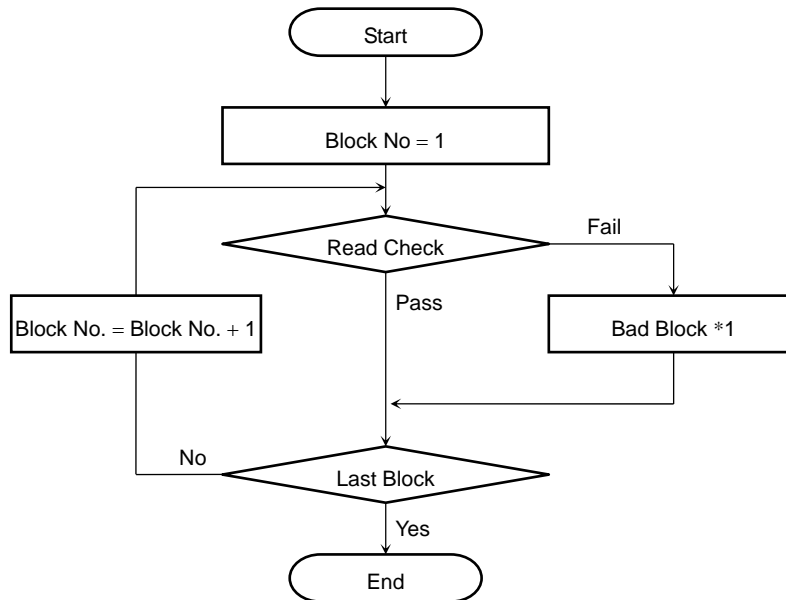
6.5. Power Off Timing

Please do not turn off the power before Write/Erase operation is complete. Avoid using the device when the battery is low. Power shortage and/or power failure before Write/Erase operation is complete will cause loss of data and/or damage to data.

6.6. Invalid Blocks

The device occasionally contains unusable blocks. Therefore, the following issues must be recognized:
Please do not perform an Erase Operation to bad blocks. It may be impossible to recover the bad block information if the information is erased. Check if the device has any bad blocks after installation into the system. Refer to the test flow for bad block detection. Bad blocks which are detected by the test flow must be managed as unusable blocks by the system. A bad block does not affect the performance of good blocks because it is isolated from the bit lines by select gates. The number of valid blocks over the device lifetime is as Table 2.

Regarding invalid blocks, the bad block mark is in the whole page. Please read one column of any page in each block. If the data of the column is 00 (Hex), define the block as a bad block.



*1: No erase operation is allowed to detected bad blocks.

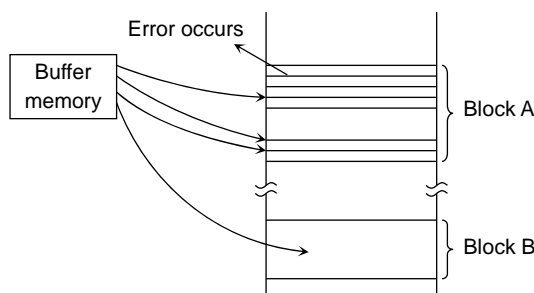
6.7. Failure Phenomena for Program and Erase Operations

The device may fail during a Program or Erase operation.
The following possible failure modes should be considered when implementing a highly reliable system.

FAILURE MODE		DETECTION AND COUNTERMEASURE SEQUENCE
Block	Erase Failure	Status Read after Erase → Block Replacement
Page	Programming Failure	Status Read after Program → Block Replacement
Read	Bit Error	ECC Correction / Block Refresh

- ECC: Error Correction Code. 8 bit correction per 512 Bytes is necessary.
- Block Replacement

Program



When an error happens in Block A, try to reprogram the data into another Block (Block B) by loading from an external buffer. Then, prevent further system accesses to Block A (by creating a bad block table or by using another appropriate scheme).

Erase

When an error occurs during an Erase Operation, prevent future accesses to this bad block (again by creating a table within the system or by using another appropriate scheme).

6.8. Reliability Guidance

This reliability guidance is intended to notify some guidance related to using NAND flash with 8 bit ECC for each 512 bytes. For detailed reliability data, please refer to TOSHIBA's reliability note. Although random bit errors may occur during use, it does not necessarily mean that a block is bad. Generally, a block should be marked as bad when a program status failure or erase status failure is detected. The other failure modes may be recovered by a block erase. ECC treatment for read data is mandatory due to the following Data Retention and Read Disturb failures.

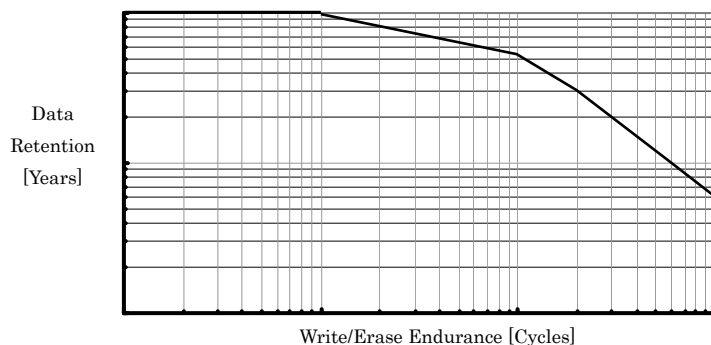
- **Write/Erase Endurance**

Write/Erase endurance failures may occur in a cell, page, or block, and are detected by doing a status read after either an Auto Program or Auto Block Erase operation. The cumulative bad block count will increase along with the number of write/erase cycles.

- **Data Retention**

The data in memory may change after a certain amount of storage time. This is due to charge loss or charge gain. After block erasure and reprogramming, the block may become usable again.

Here is the combined characteristics image of Write/Erase Endurance and Data Retention.



- **Read Disturb**

A Read Operation may disturb the data in memory. The data may change due to charge gain. Usually, bit errors occur on other pages in the block, not the page being read. After a large number of read cycles (between block erases), a tiny charge may build up and can cause a cell to be soft programmed to another state. After block erasure and reprogramming, the block may become usable again.

7. Revision History

Date	Rev.	Description
2016-06-22	1.0	Initial Release

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